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(54) **HIGHLY COMPACT EPROM AND FLASH EEPROM DEVICES**

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(51) **Int. Cl.**^{7} **G11C 11/34**
(52) **U.S. Cl.** **365/185.3**

(57) **ABSTRACT**

Structures, methods of manufacturing and methods of use of electrically programmable read only memories (EPROM) and flash electrically erasable and programmable read only memories (EEPROM) include split channel and other cell configurations. An arrangement of elements and cooperative processes of manufacture provide self-alignment of the elements. An intelligent programming technique allows each memory cell to store more than the usual one bit of information. An intelligent erase algorithm prolongs the useful life of the memory cells. Use of these various features provides a memory having a very high storage density and a long life, making it particularly useful as a solid state memory in place of magnetic disk storage devices in computer systems.

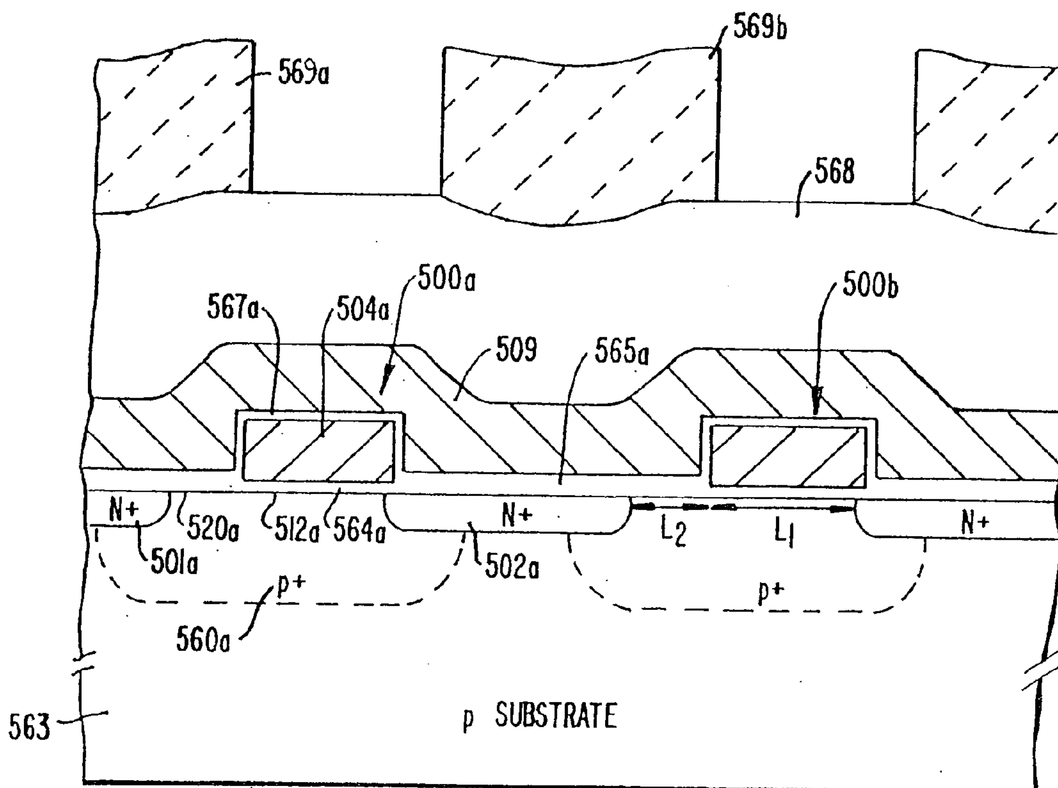

FIG. 1. PRIOR ART

FIG. 2a. PRIOR ART

FIG. 2b PRIOR ART

FIG. 3a PRIOR ART

V_{ERASE}

R

200b

230b

202b

209b

201b

204b

FIG. 2c. PRIOR ART

V_{CG}

V_{ERASE}

320

311

312

331

300

309

330

304

332

V_S

301

V_D

302

303

V_{BB}

FIG. 3b. PRIOR ART

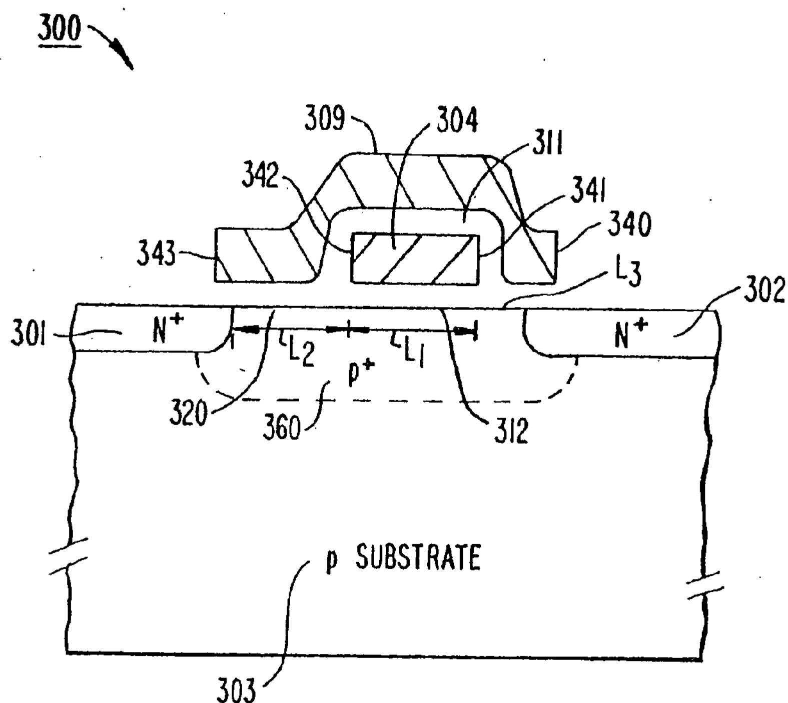

FIG. 3c. PRIOR ART

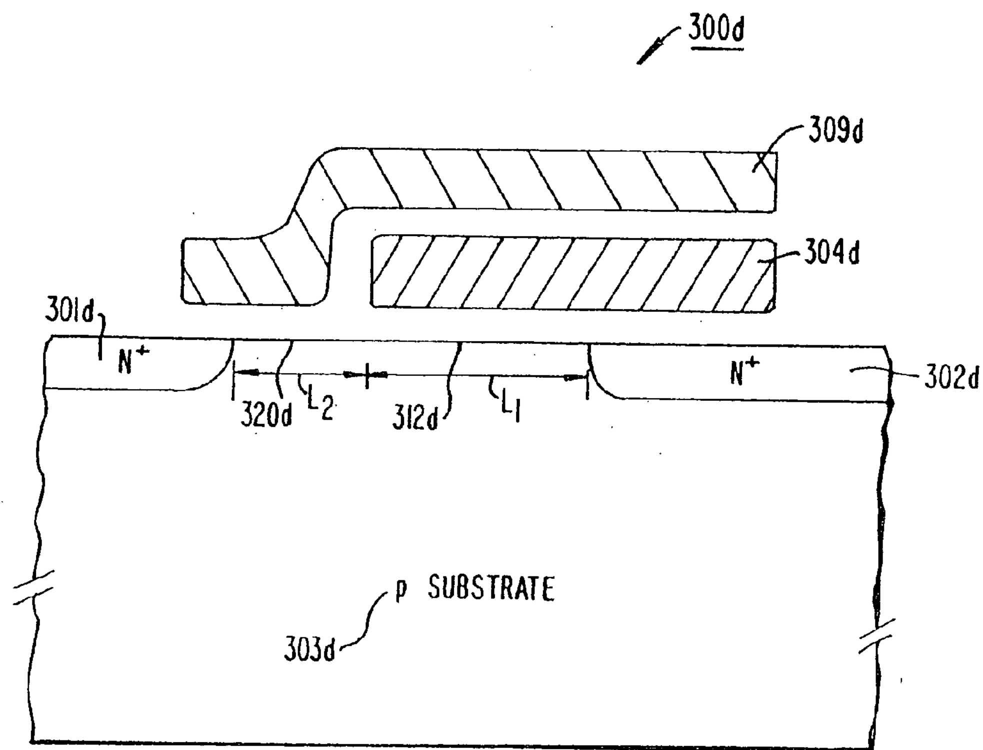

FIG. 3d. PRIOR ART

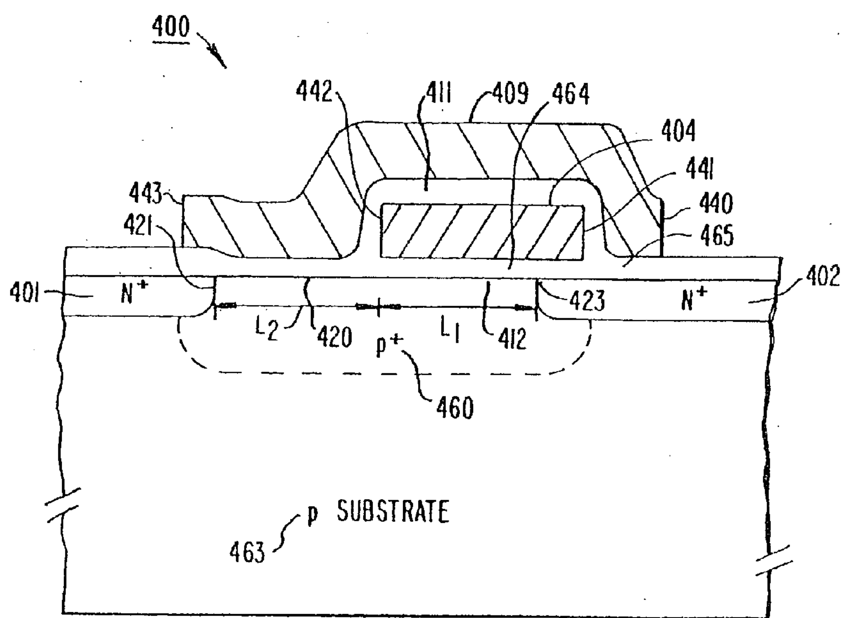

FIG. 4a. PRIOR ART

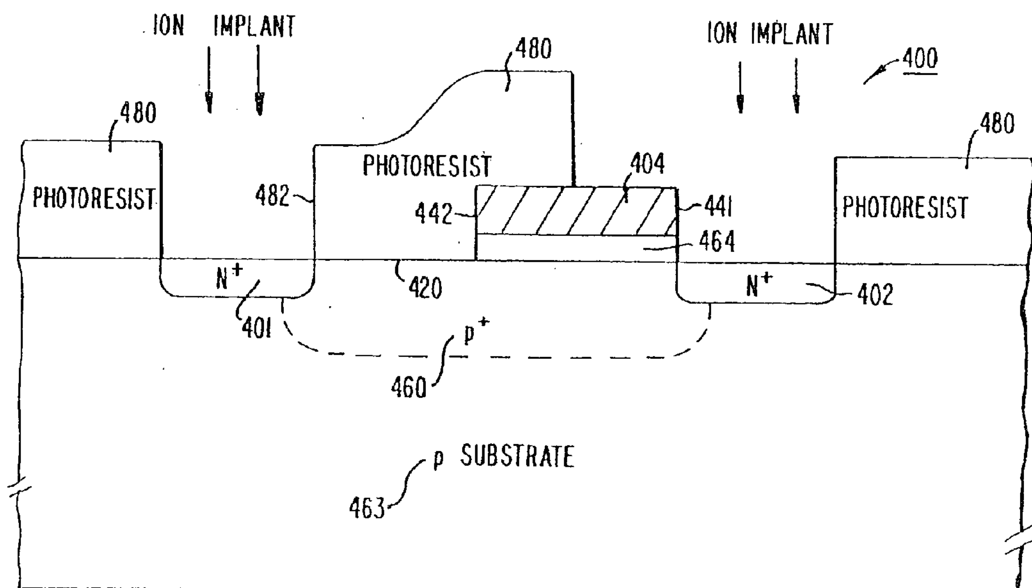

FIG. 4b. PRIOR ART

FIG. 4c. PRIOR ART

FIG. 4d. PRIOR ART

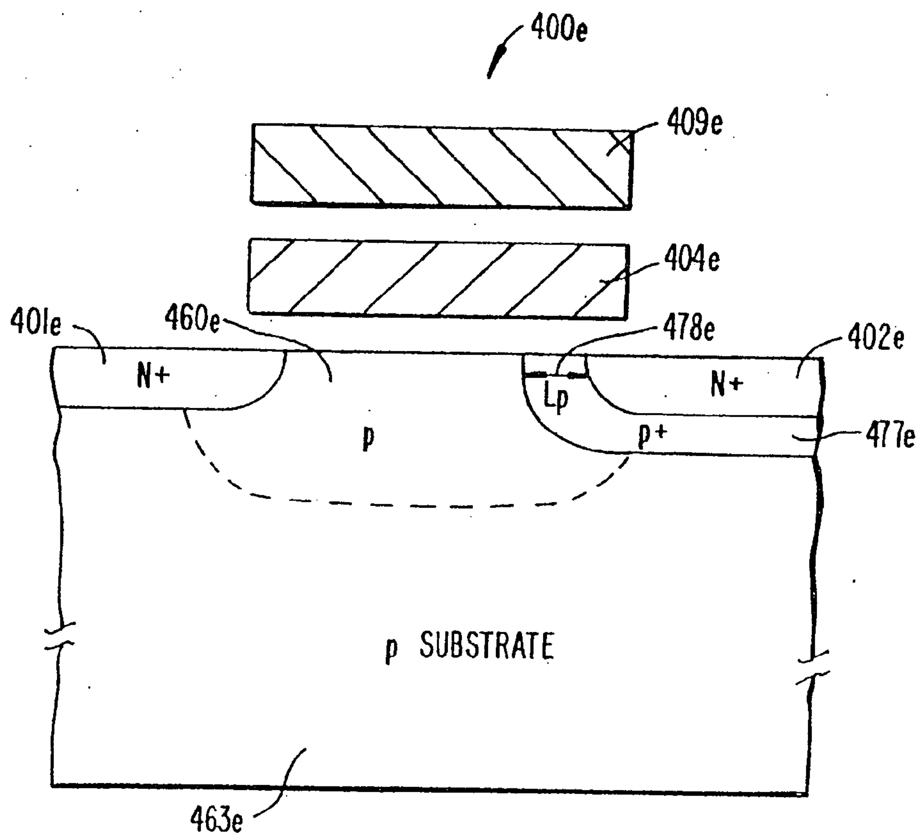

FIG.4e PRIOR ART

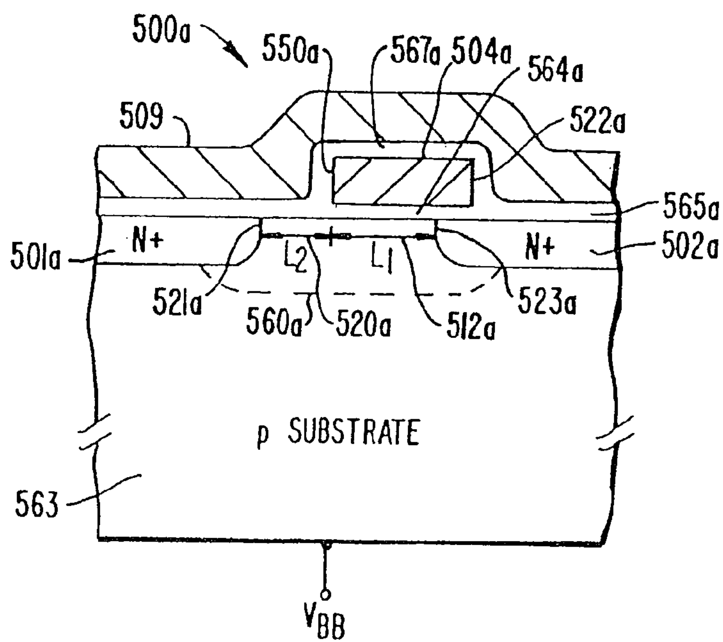

FIG.5a

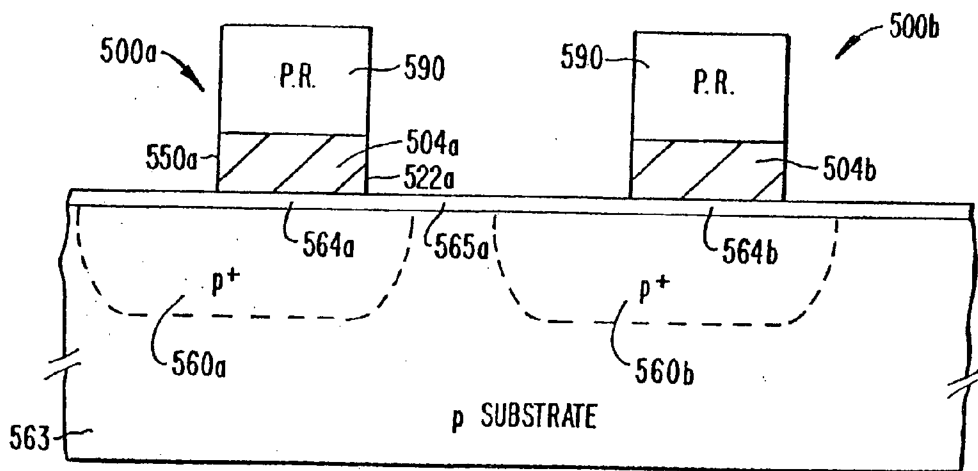

FIG. 5b

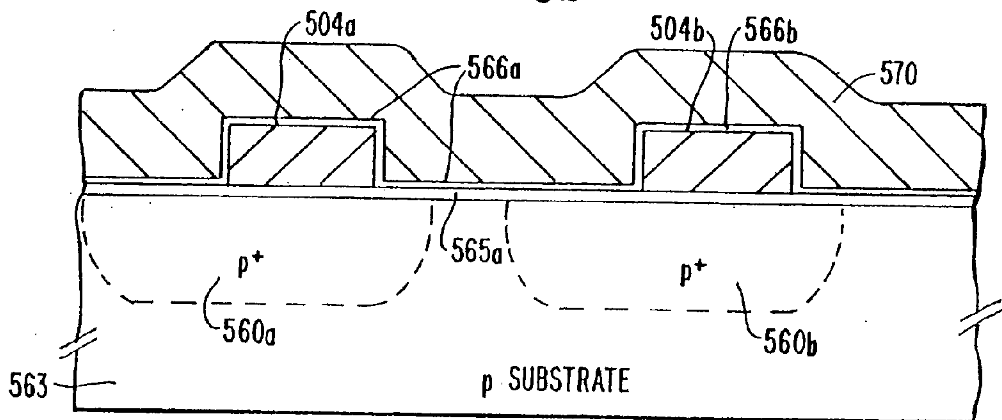

FIG. 5c

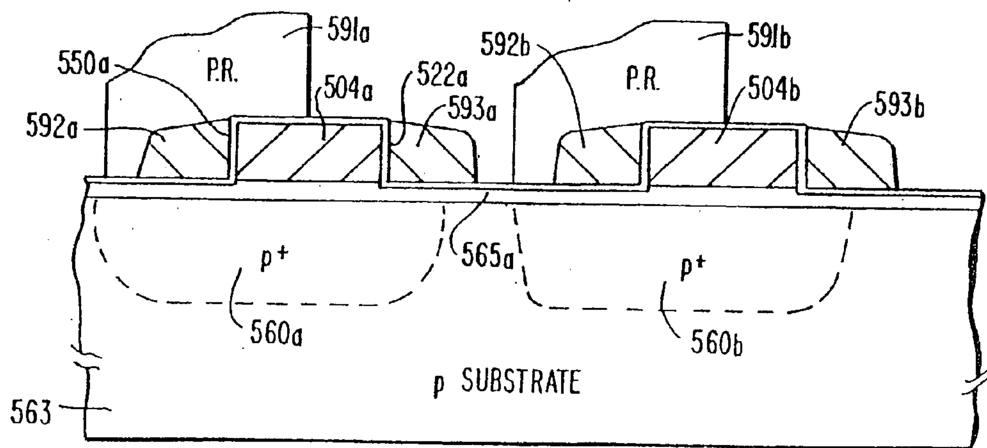

FIG. 5d

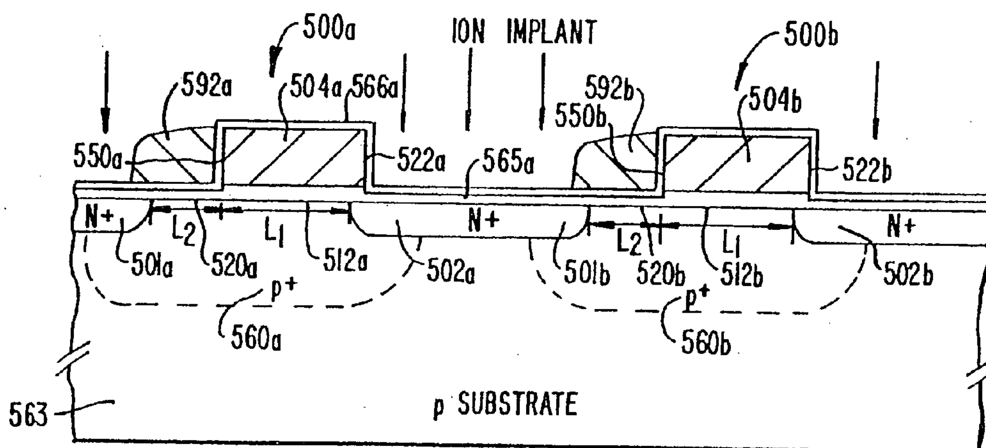

FIG.5e

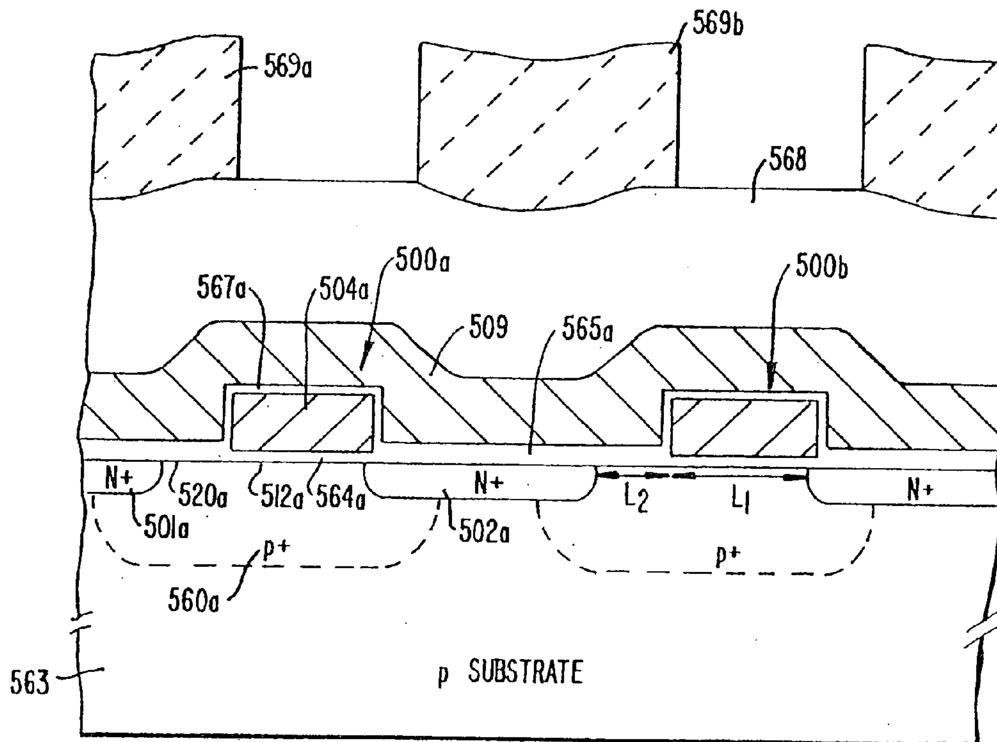

FIG.5f

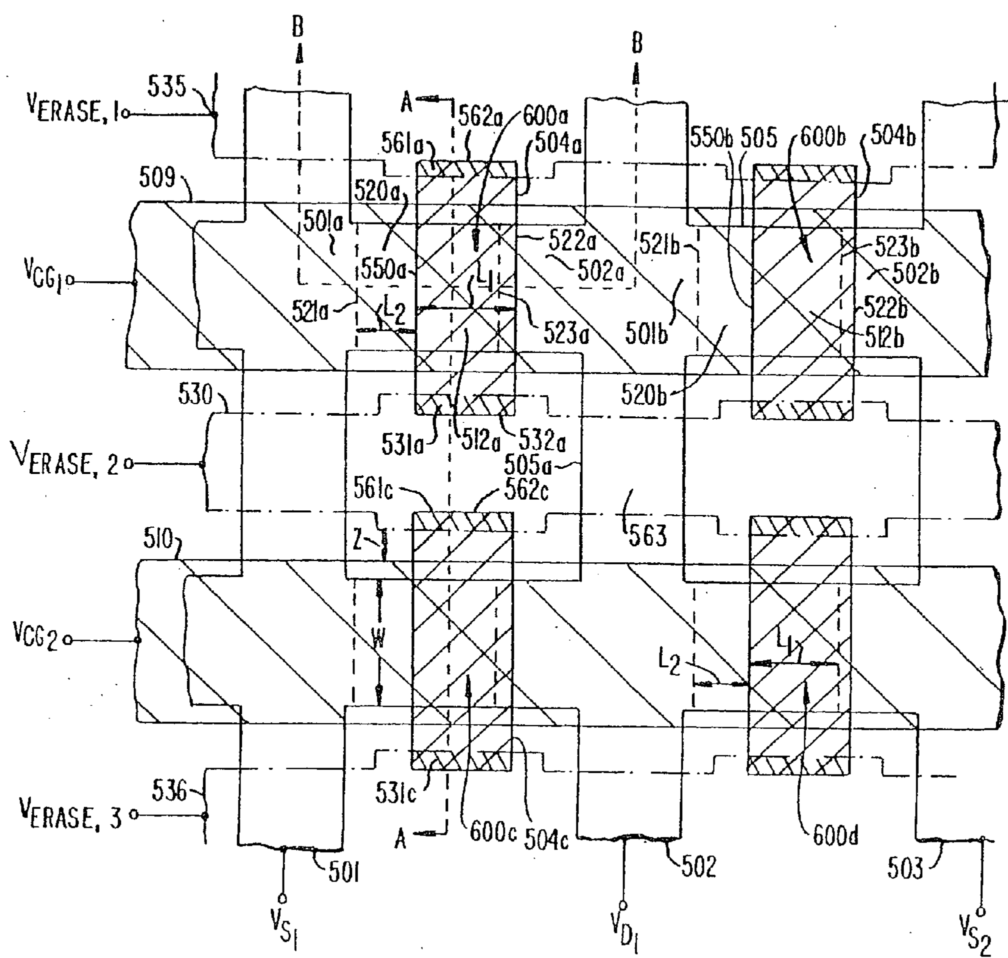

FIG.6a

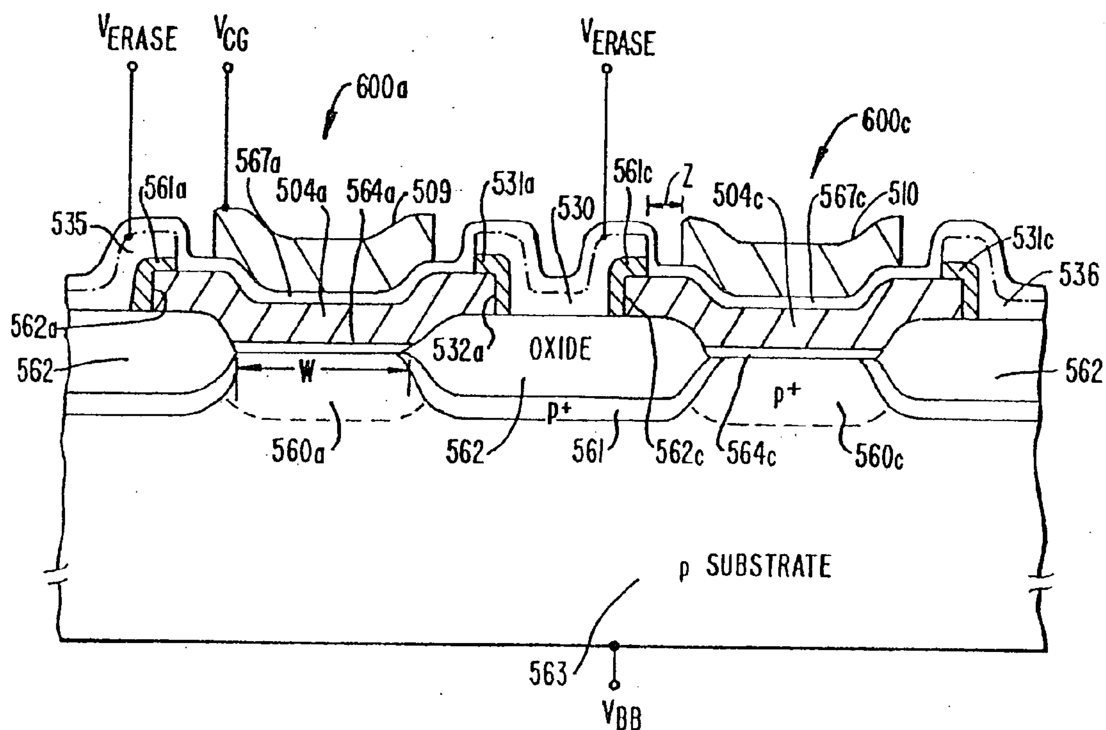

FIG. 6b

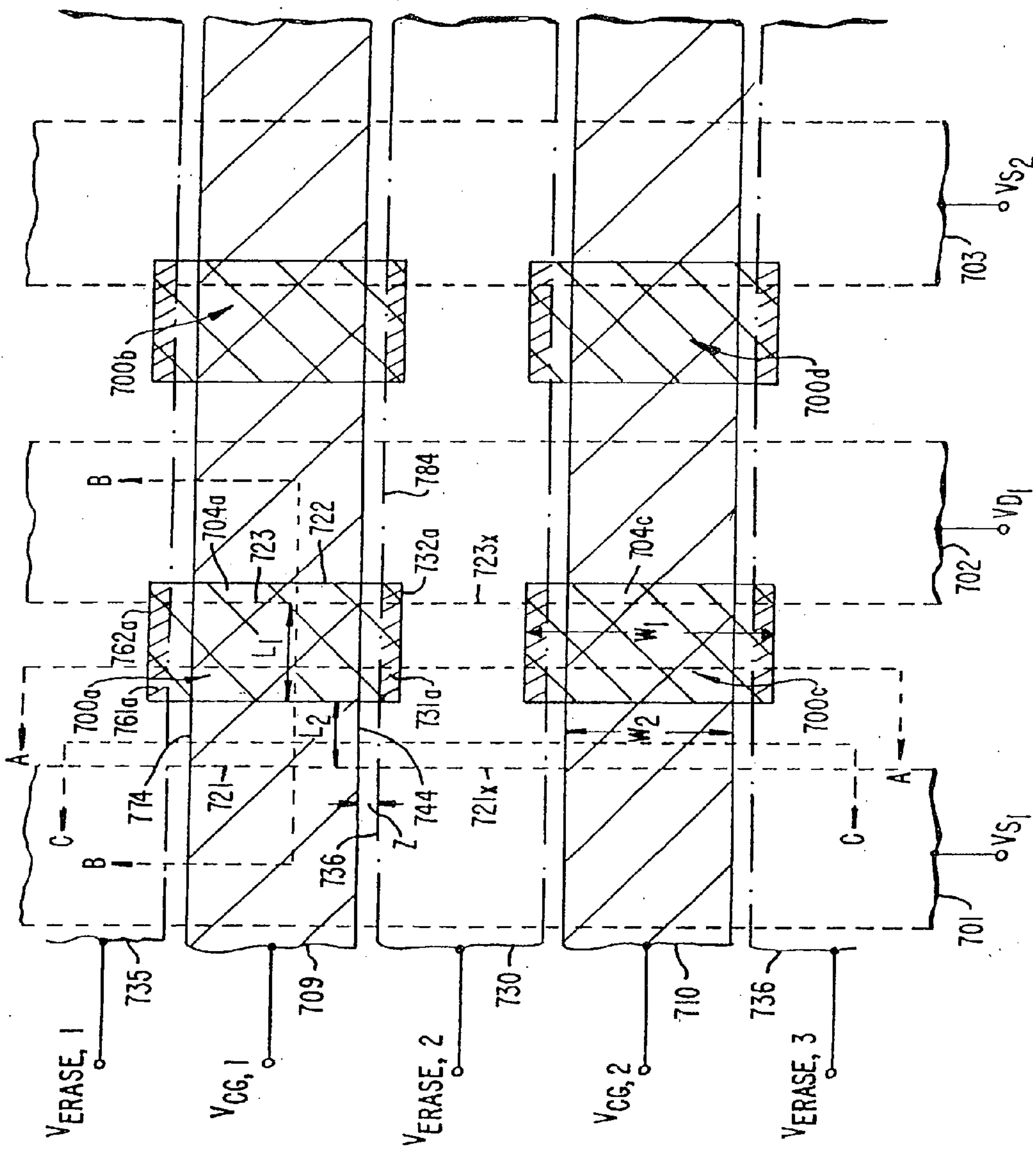

FIG. 7a

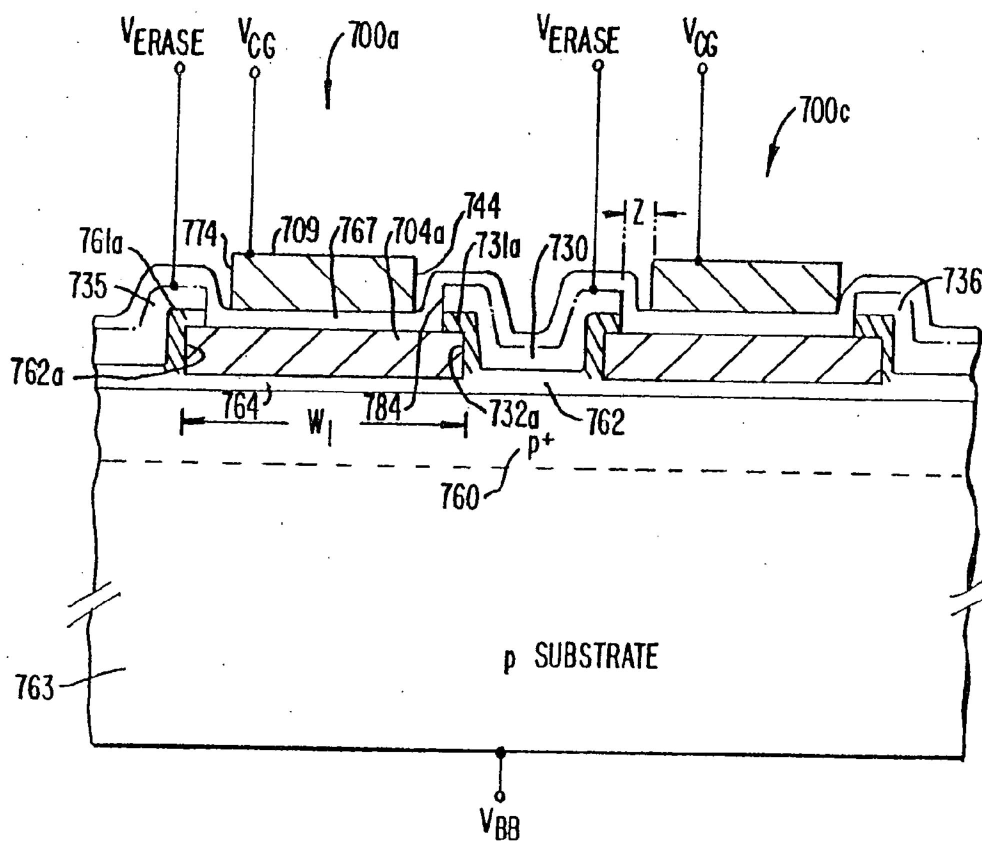

FIG. 7b

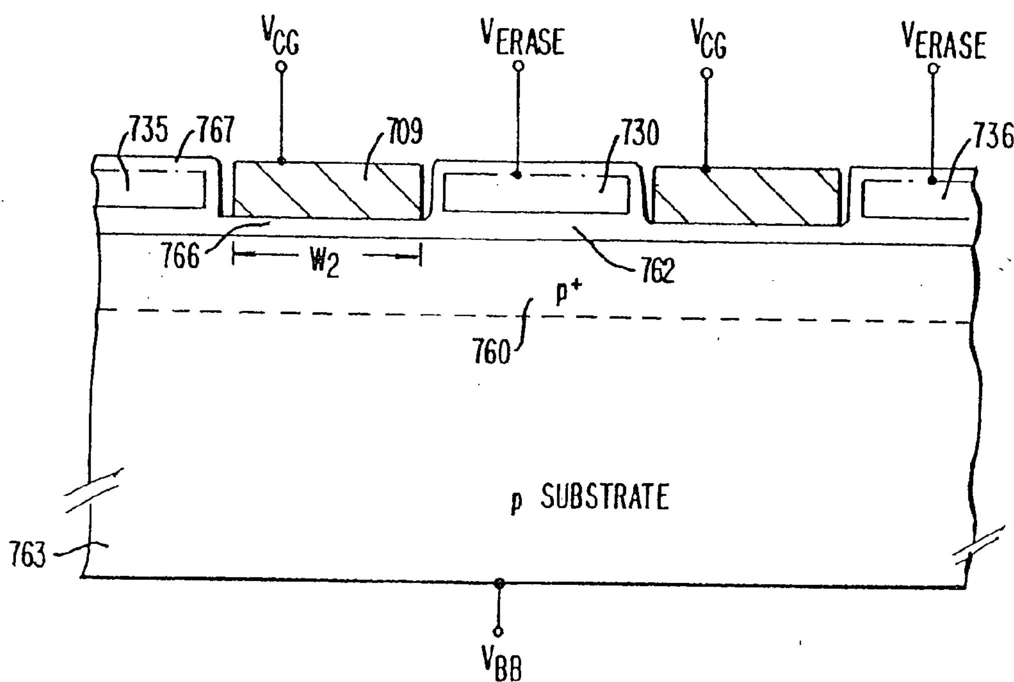

FIG. 7c

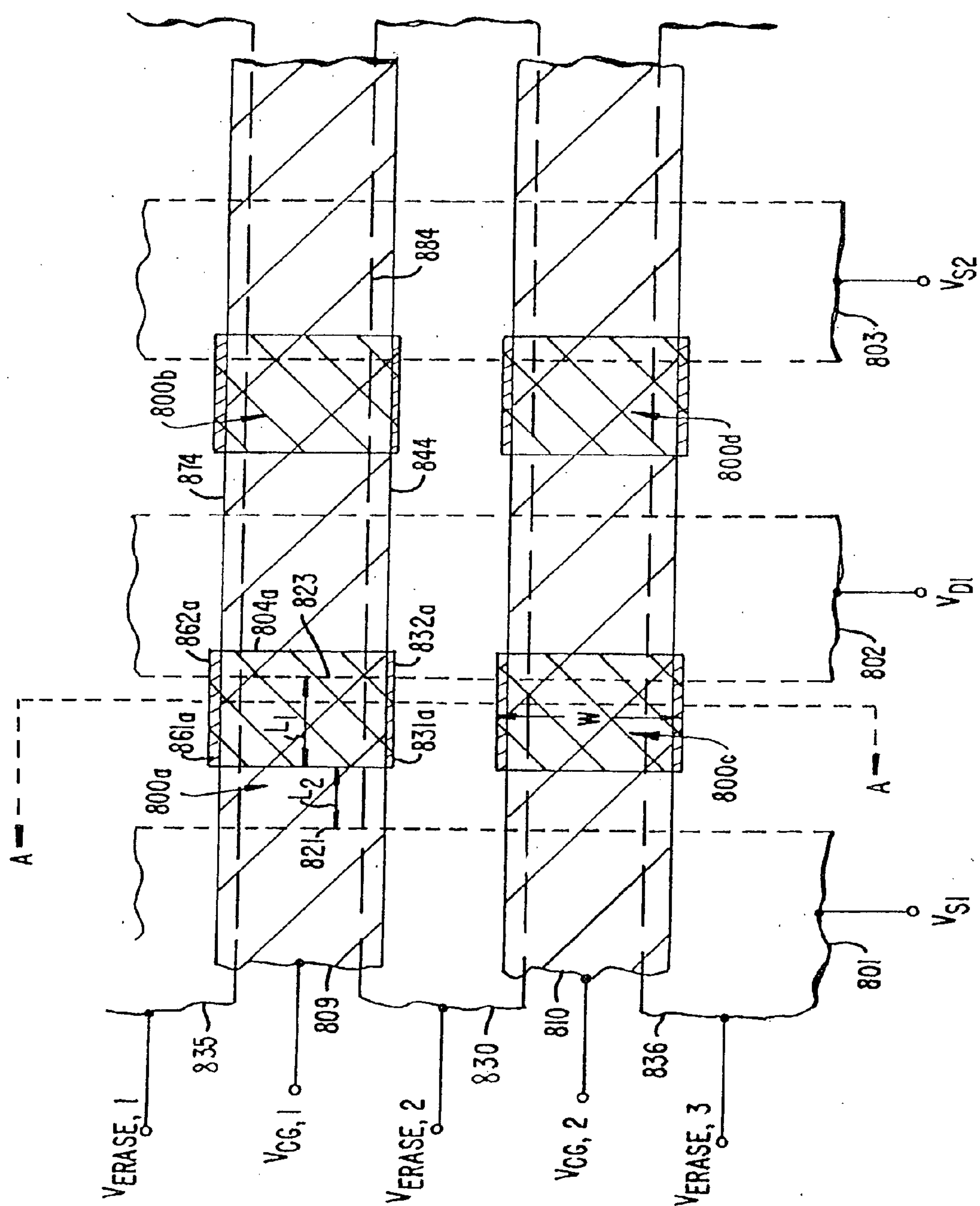

FIG.8a

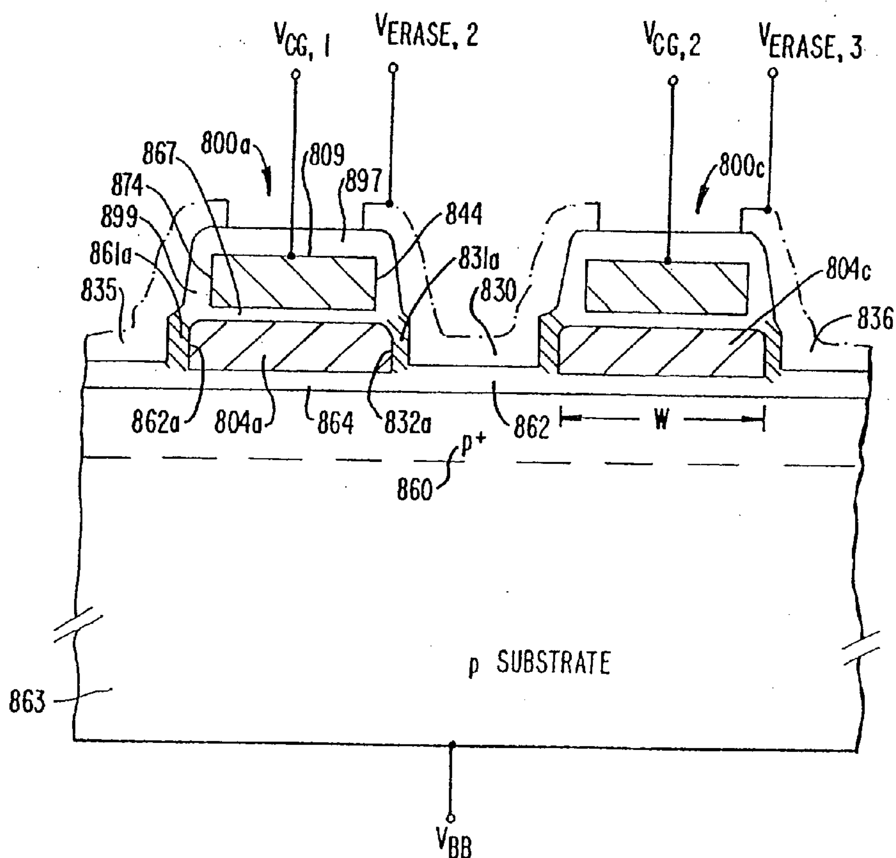

FIG. 8b

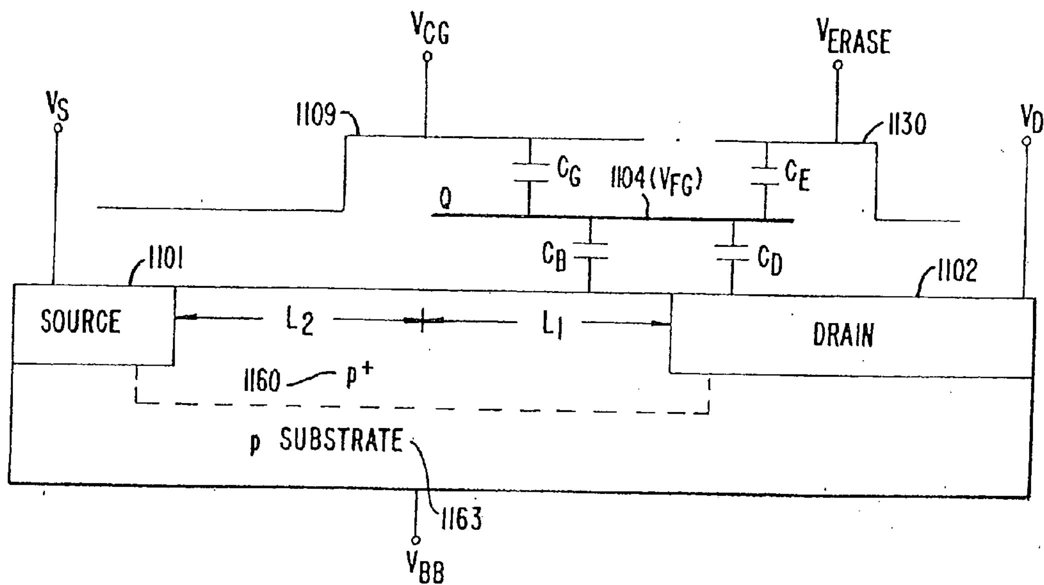

FIG. 10

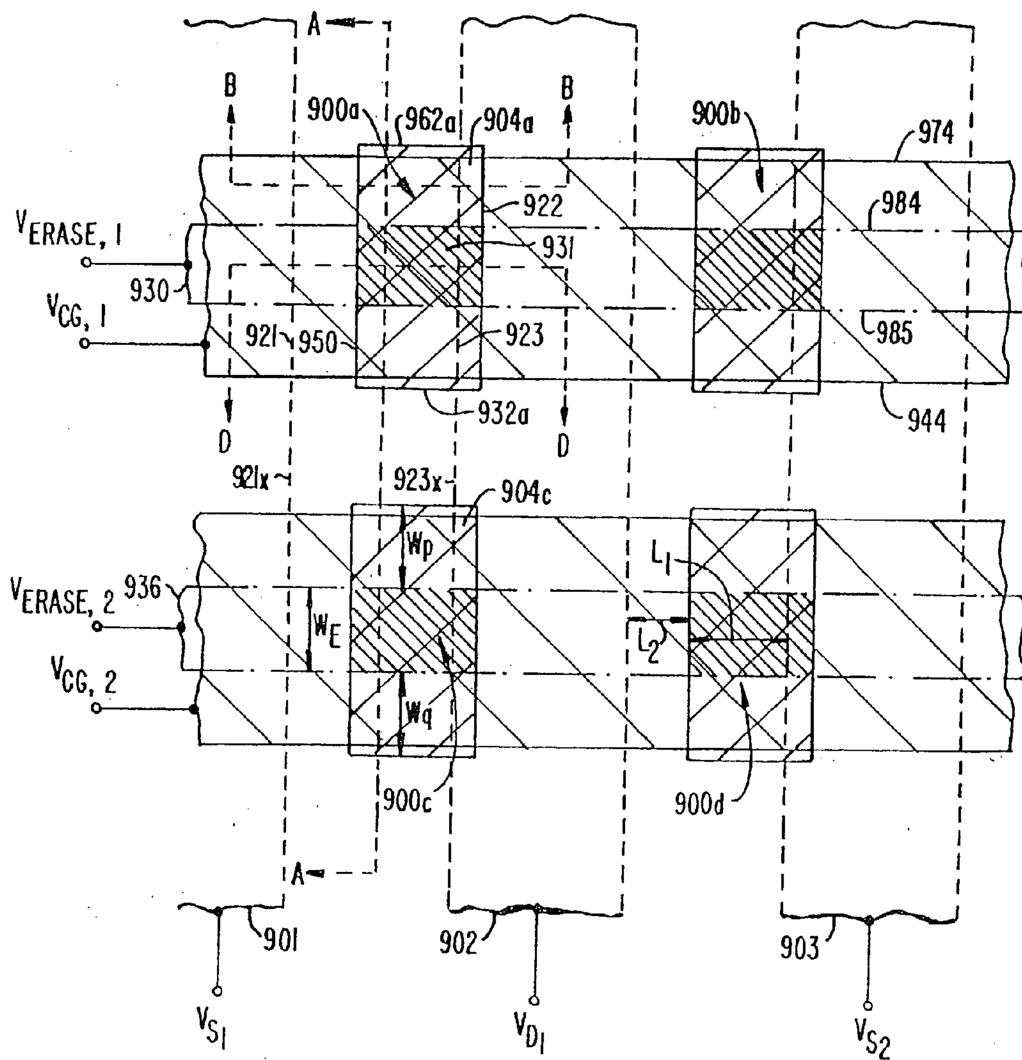

FIG. 9a

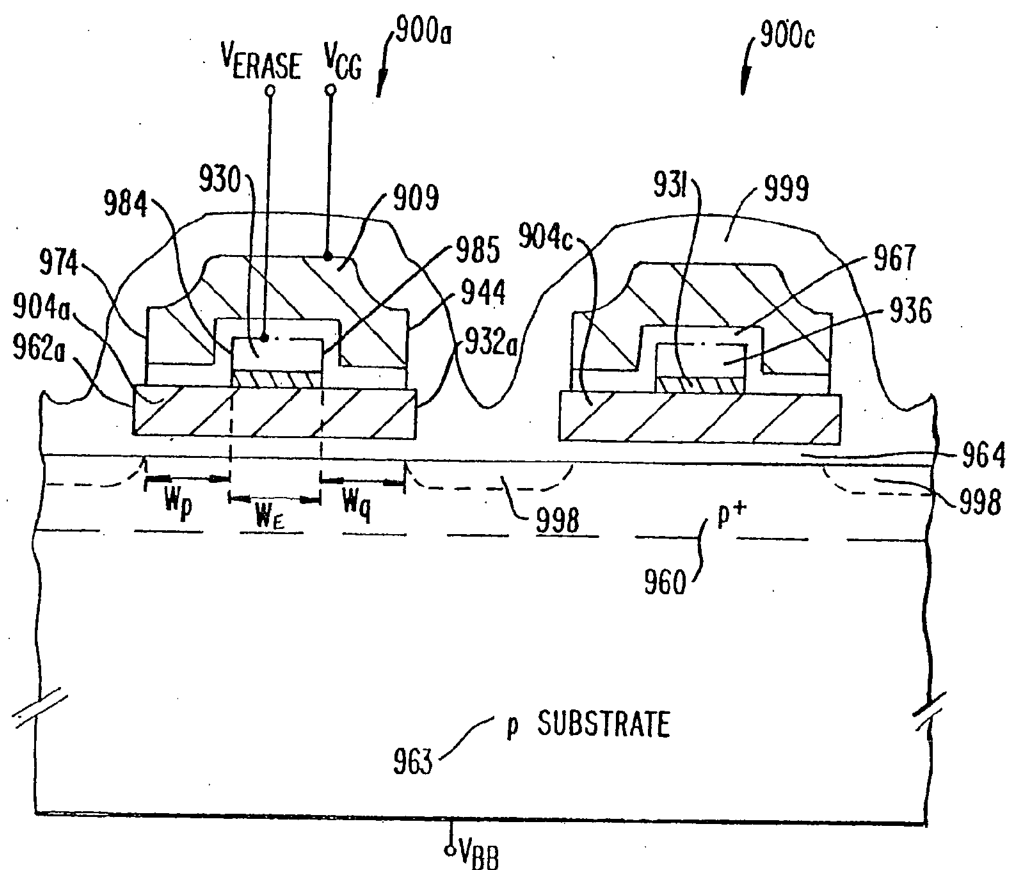

FIG. 9b

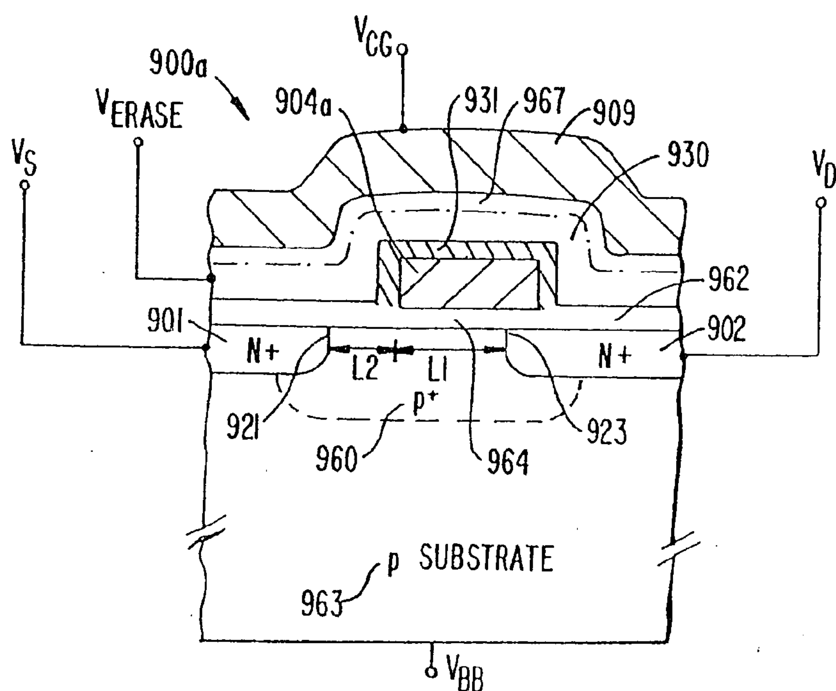

FIG. 9c

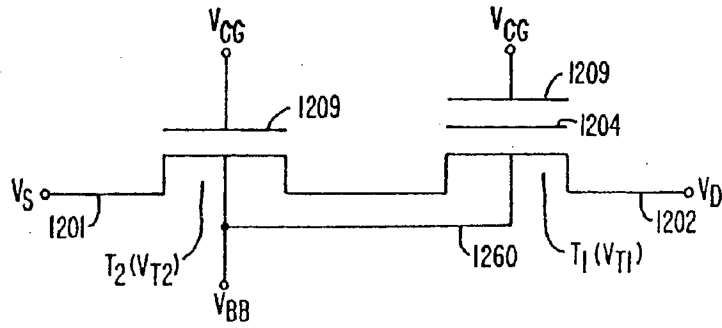

FIG. 11a

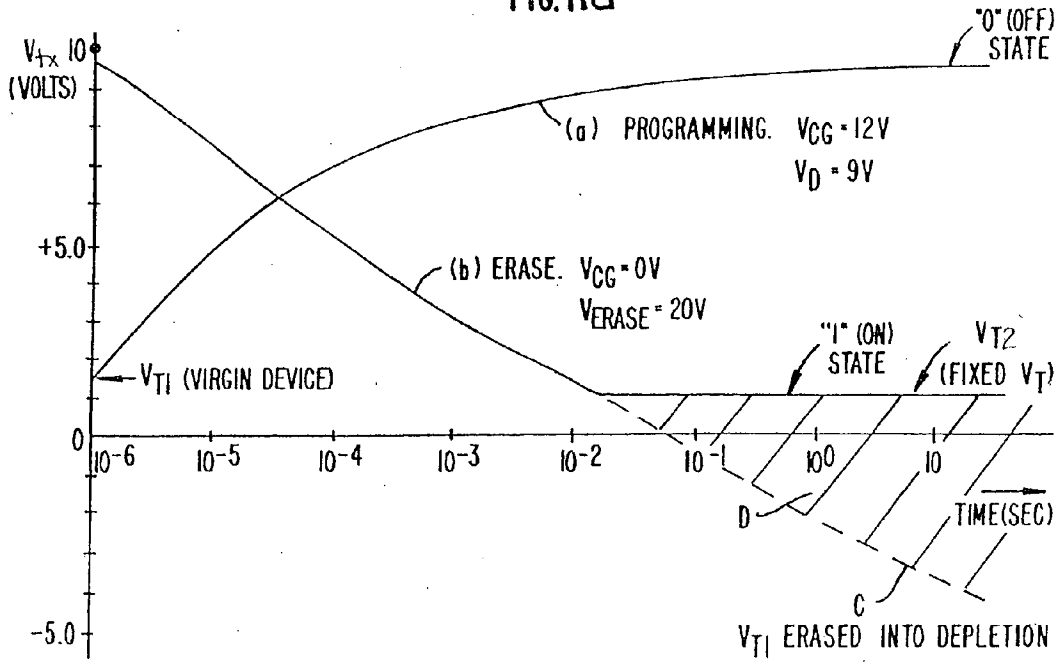

FIG. 11b

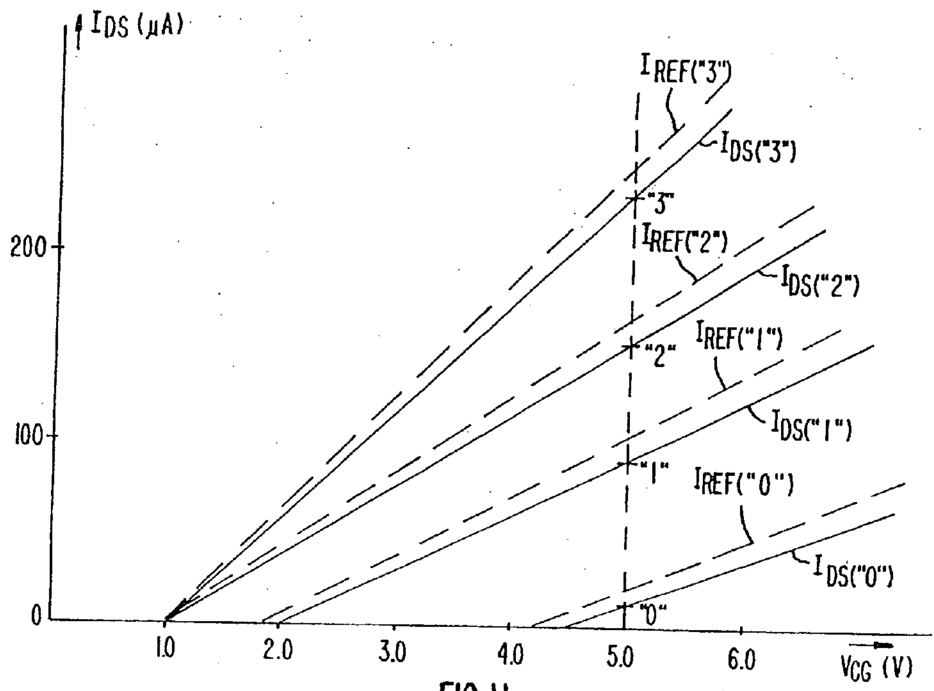

FIG. 11c

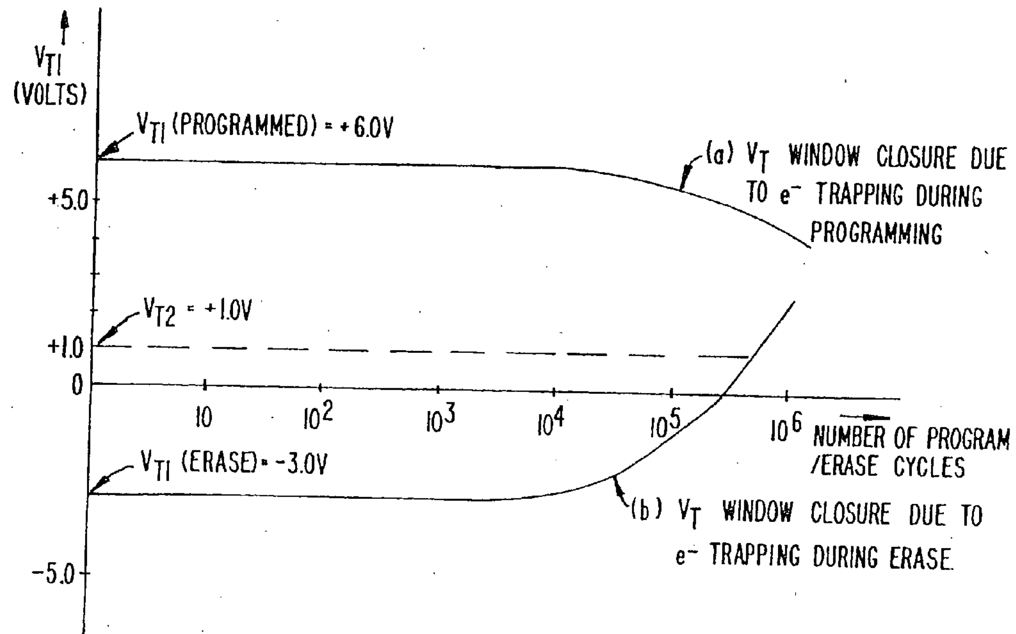

FIG. 11d

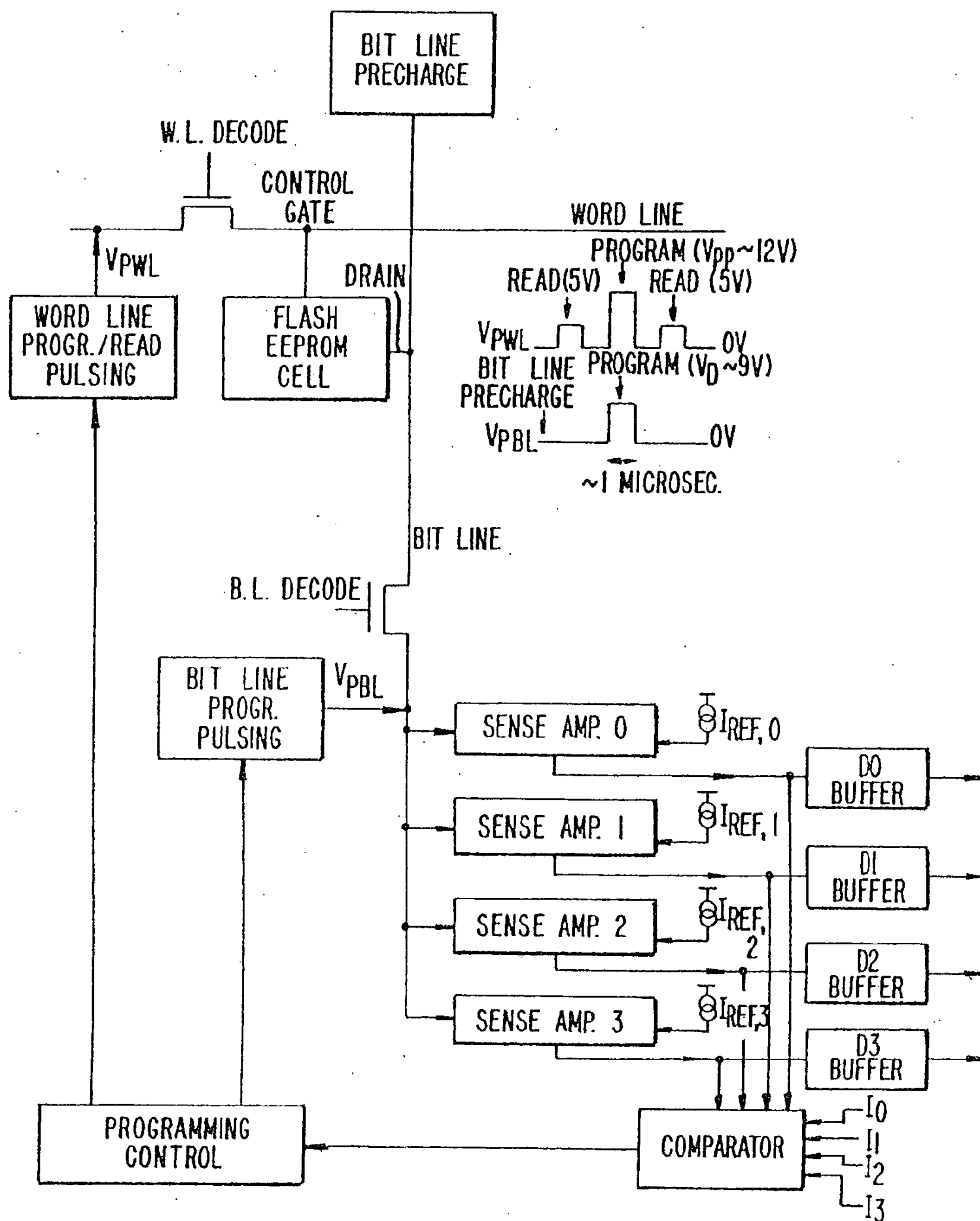

FIG. 11e

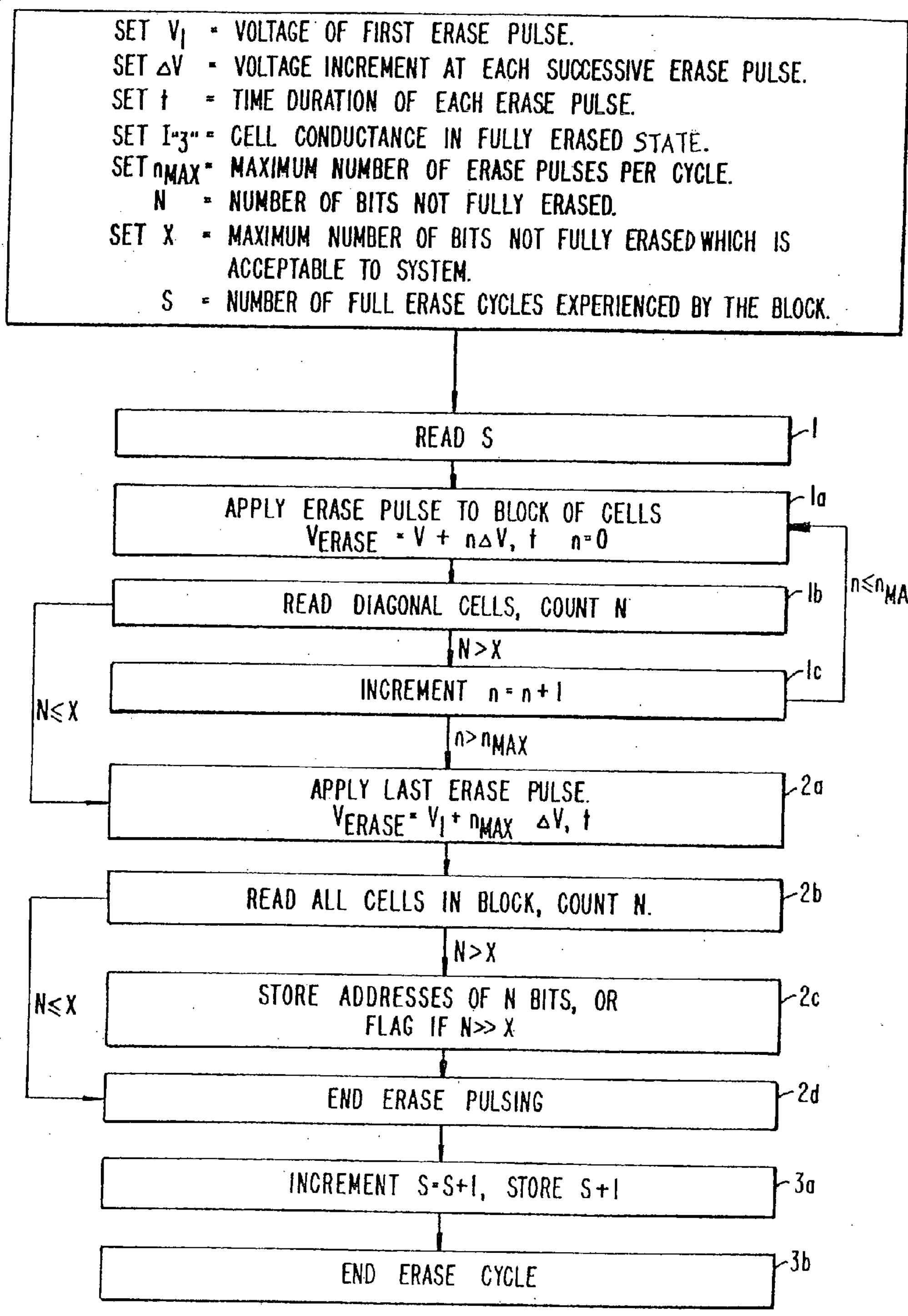

FIG. 12

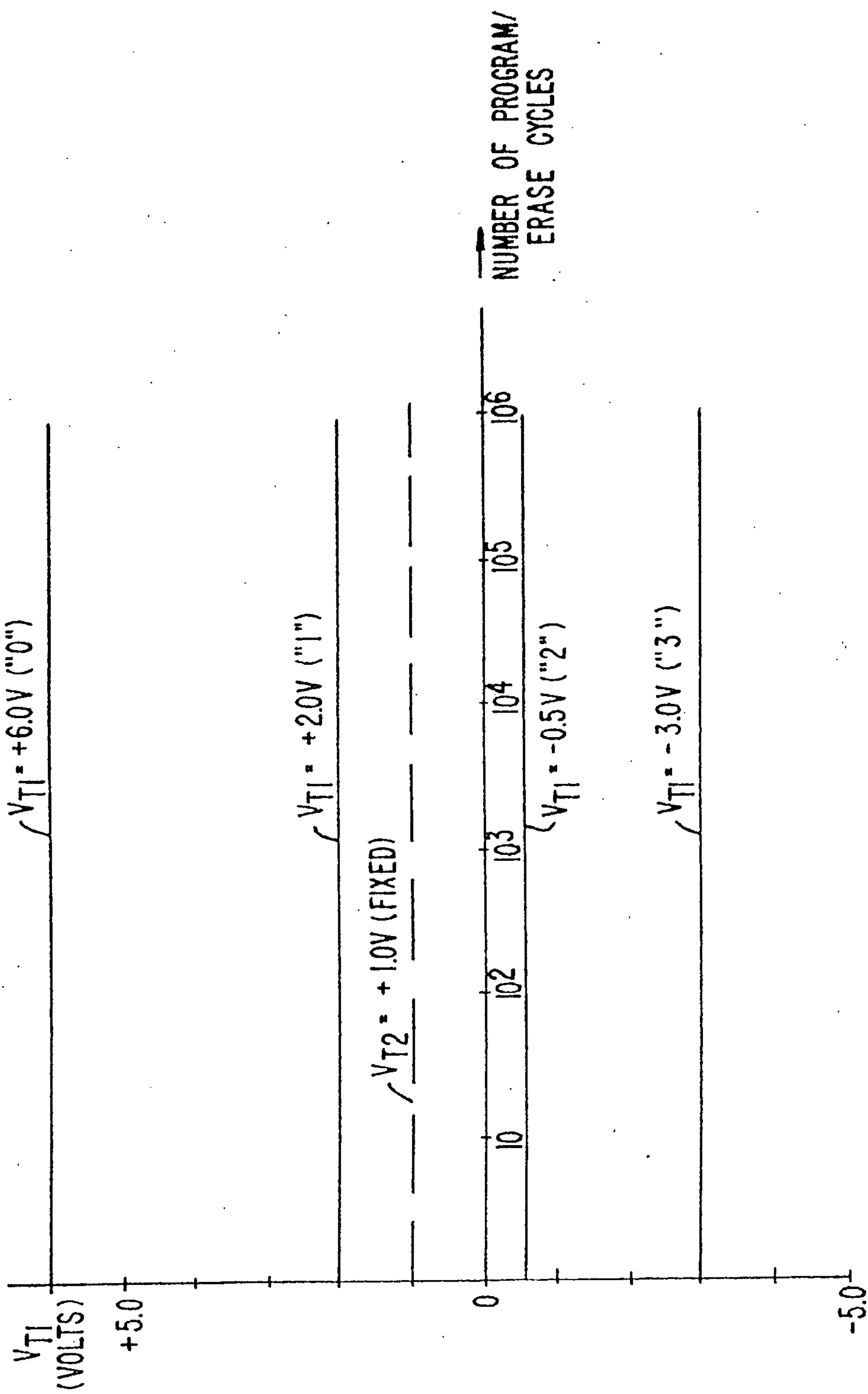

FIG. 13

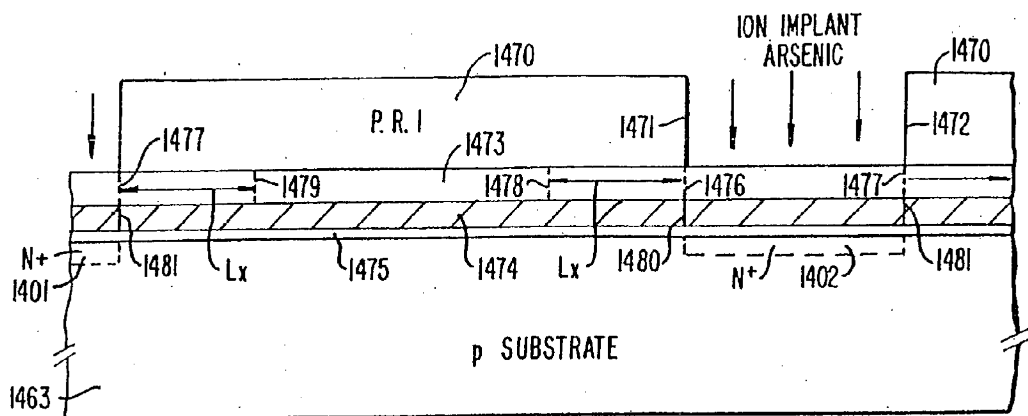

FIG. 14a

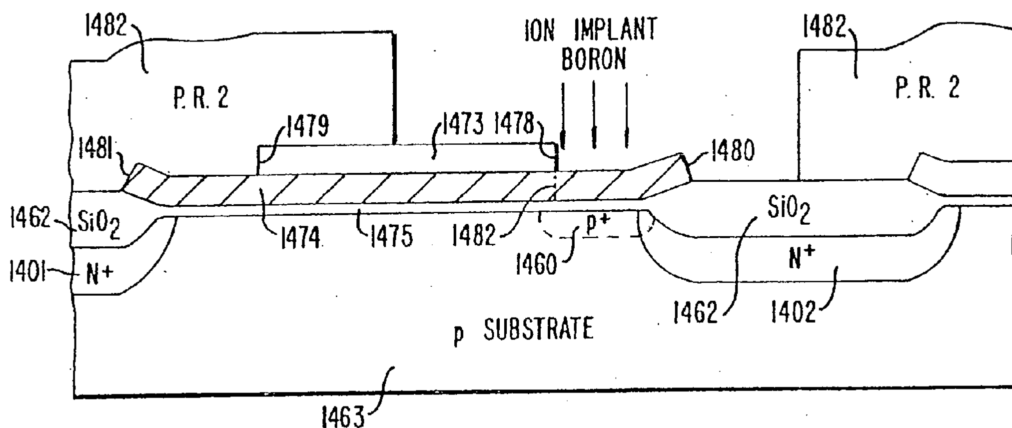

FIG. 14b

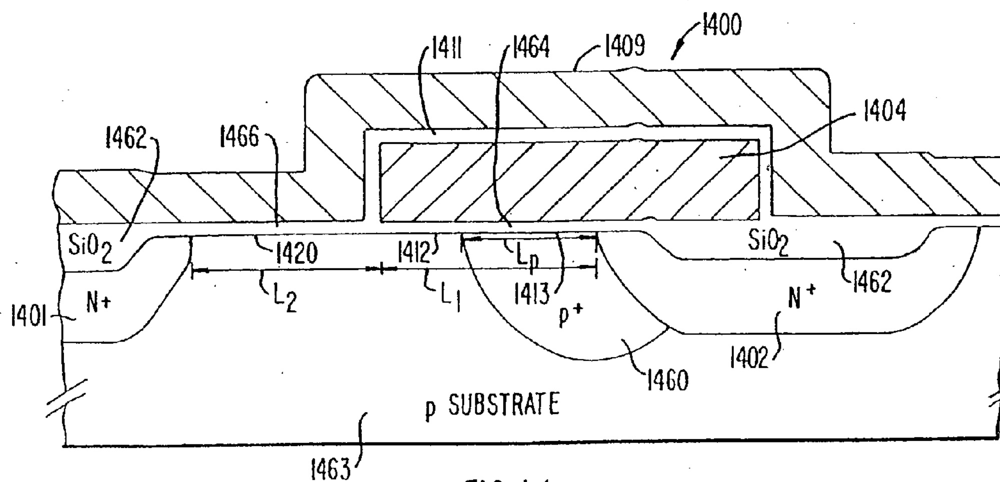

FIG. 14c

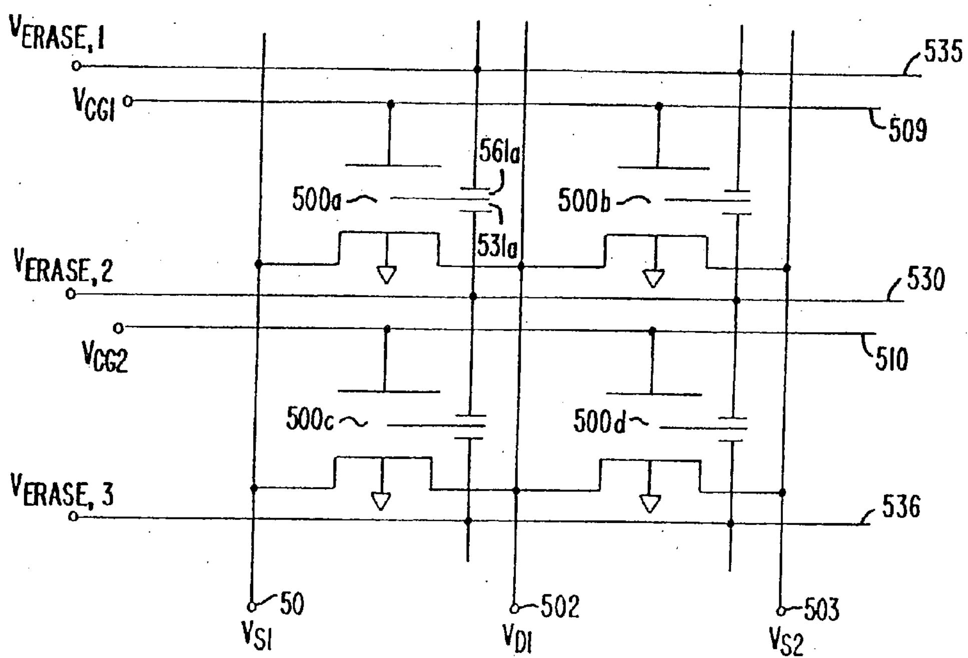

FIG. 15b

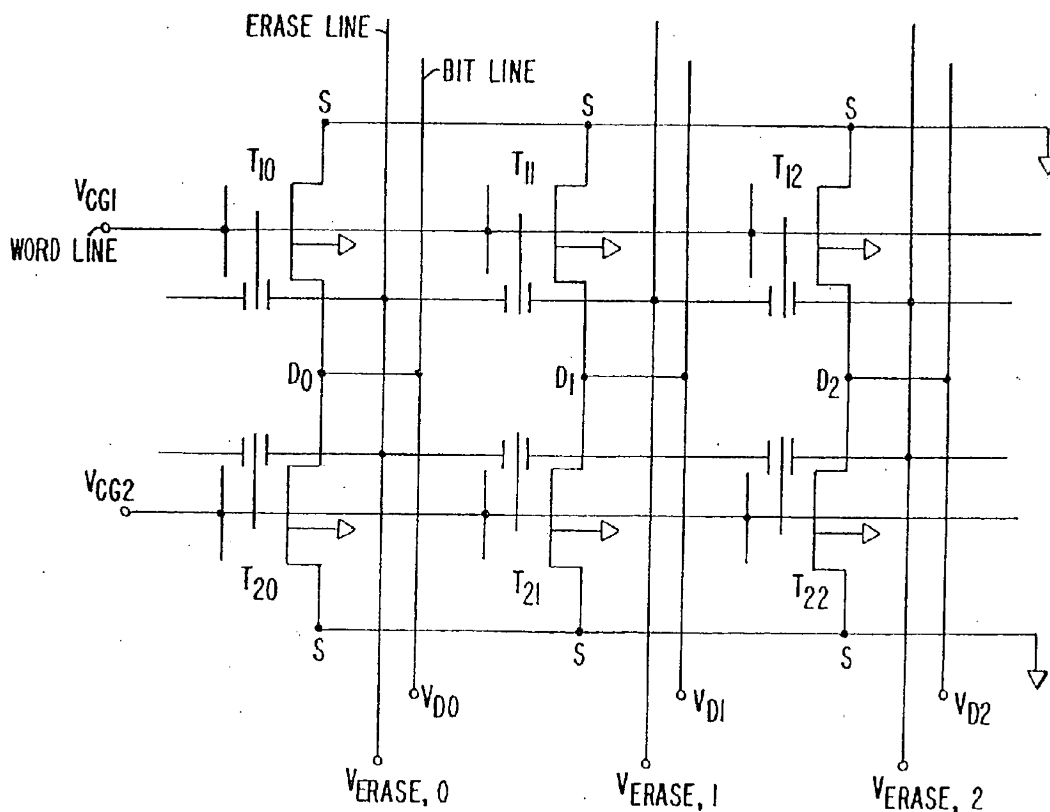

FIG. 15a

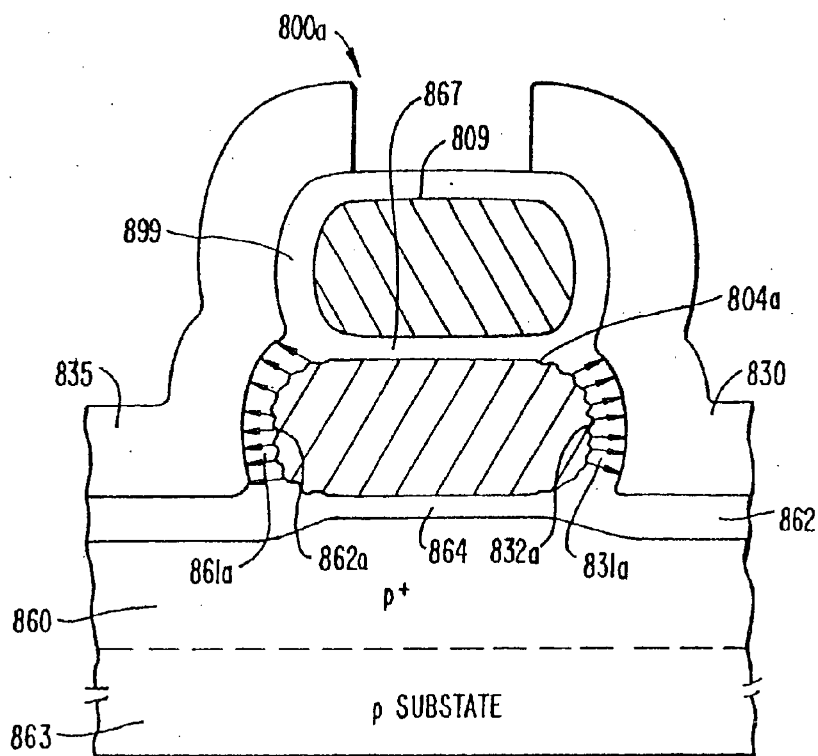

FIG.16a

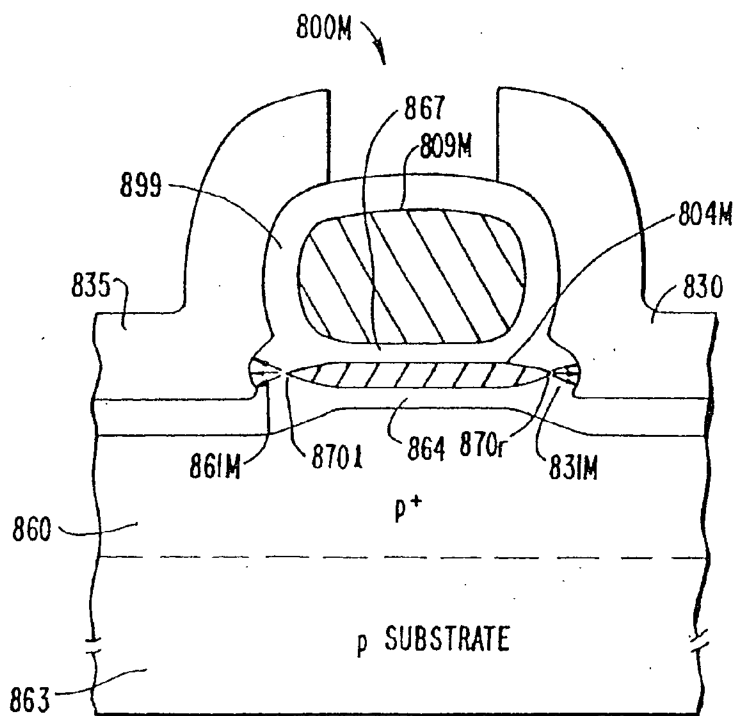

FIG.16b

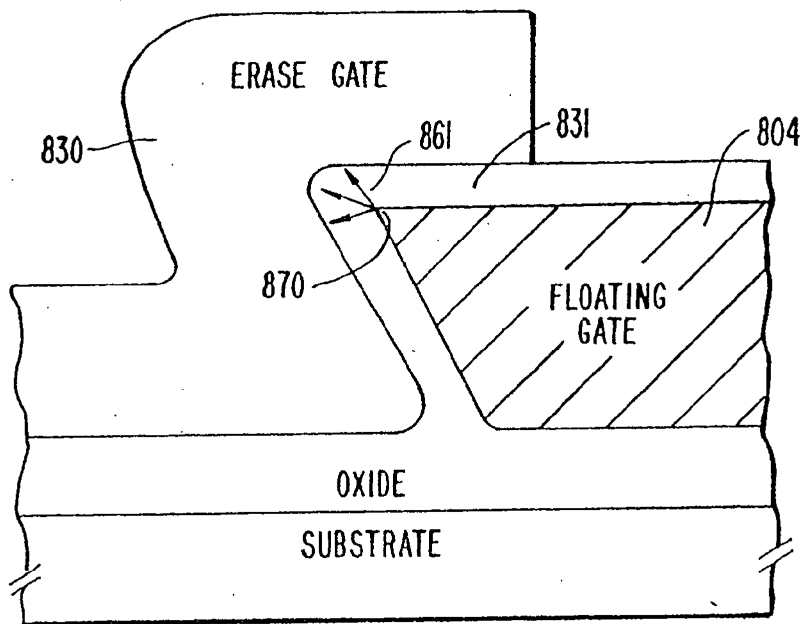

FIG. 16c

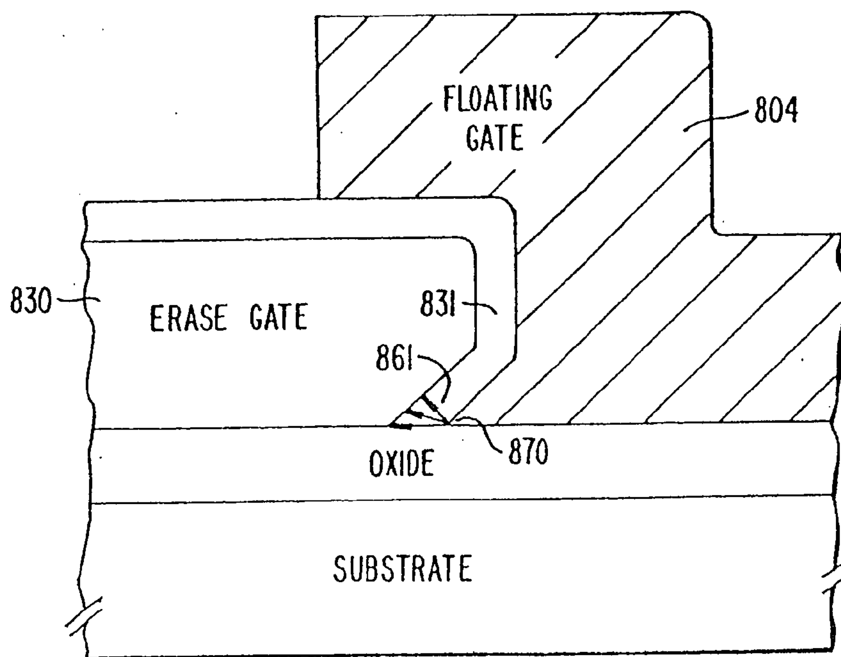

FIG. 16d

TABLE I. ARRAY OF FIGURE 15a.

	V_{CG}			V_D			S			V_{ERASE}		
	SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL	
		SAME ROW	SAME COL.		SAME ROW	SAME COL.		SAME ROW	SAME COL.		SAME ROW	SAME COL.
READ	5V	5V	0V	1.5V	0V	1.5V	0V	0V	0V	0V	0V	0V
ERASE	0V	0V	0V	0V	0V	0V	0V	0V	0V	20V	20V (BLOCK	20V ERASE)
PROGRAM	12V	12V	0V	8V	0V	8V	0V	0V	0V	0V	0V	0V

FIG. 17a

TABLE II. VIRTUAL GROUND ARRAY OF FIGURE 15b.

	V_{CG}			V_D			S			V_{ERASE}		
	SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL		SEL. CELL	UNSEL. CELL	
		SAME ROW	SAME COL.		SAME ROW	SAME COL.		SAME ROW	SAME COL		SAME ROW	SAME COL
READ	5V	5V	0V	1.5V	1.5V	1.5V	0V	1.5V	0V	0V	0V	0V
ERASE	0V	0V	0V	0V	0V	0V	0V	0V	0V	20V	20V (BLOCK	20V ERASE)
PROGRAM	12V	12V	0V	8V	FLOAT	8V	~0V	FLOAT	~0V	0V	0V	0V

FIG. 17b

HIGHLY COMPACT EPROM AND FLASH EEPROM DEVICES

BACKGROUND OF THE INVENTION

[0001] This invention relates generally to semi-conductor electrically programmable read only memories (Eprom) and electrically erasable programmable read only memories (EEprom), and specifically to semiconductor structures of such memories, processes of making them, and techniques for using them.

[0002] An electrically programmable read only memory (Eprom) utilizes a floating (unconnected) conductive gate, in a field effect transistor structure, positioned over but insulated from a channel region in a semi-conductor substrate, between source and drain regions. A control gate is then provided over the floating gate, but also insulated therefrom. The threshold voltage characteristic of the transistor is controlled by the amount of charge that is retained on the floating gate. That is, the minimum amount of voltage (threshold) that must be applied to the control gate before the transistor is turned "on" to permit conduction between its source and drain regions is controlled by the level of charge on the floating gate. A transistor is programmed to one of two states by accelerating electrons from the substrate channel region, through a thin gate dielectric and onto the floating gate.

[0003] The memory cell transistor's state is read by placing an operating voltage across its source and drain and on its control gate, and then detecting the level of current flowing between the source and drain as to whether the device is programmed to be "on" or "off" at the control gate voltage selected. A specific, single cell in a two-dimensional array of Eprom cells is addressed for reading by application of a source-drain voltage to source and drain lines in a column containing the cell being addressed, and application of a control gate voltage to the control gates in a row containing the cell being addressed.

[0004] This type of Eprom transistor is usually implemented in one of two basic configurations. One is where the floating gate extends substantially entirely over the transistor's channel region between its source and drain. Another type, preferred in many applications, is where the floating gate extends from the drain region only part of the way across the channel. The control gate then extends completely across the channel, over the floating gate and then across the remaining portion of the channel not occupied by the floating gate. The control gate is separated from that remaining channel portion by a thin gate oxide. This second type is termed a "split-channel" Eprom transistor. This results in a transistor structure that operates as two transistors in series, one having a varying threshold in response to the charge level on the floating gate, and another that is unaffected by the floating gate charge but rather which operates in response to the voltage on the control gate as in any normal field effect transistor.

[0005] Early Eprom devices were erasable by exposure to ultraviolet light. More recently, the transistor cells have been made to be electrically erasable, and thus termed electrically erasable and programmable read only memory (EEprom). One way in which the cell is erased electrically is by transfer of charge from the floating gate to the transistor drain through a very thin tunnel dielectric. This is accomplished by application of appropriate voltages to the transistor's source, drain and control gate. Other EEprom memory cells are provided with a separate, third gate for accomplishing the erasing. An erase gate passes through each memory cell transistor closely adjacent to a surface of the floating gate but insulated therefrom by a thin tunnel dielectric. Charge is then removed from the floating gate of a cell to the erase gate, when appropriate voltages are applied to all the transistor elements. An array of EEprom cells are generally referred to as a Flash EEprom array because an entire array of cells, or significant group of cells, is erased simultaneously (i.e., in a flash).

[0006] EEprom's have been found to have a limited effective life. The number of cycles of programming and erasing that such a device can endure before becoming degraded is finite. After a number of such cycles in excess of 10,000, depending upon its specific structure, its programmability can be reduced. Often, by the time the device has been put through such a cycle for over 100,000 times, it can no longer be programmed or erased properly. This is believed to be the result of electrons being trapped in the dielectric each time charge is transferred to or away from the floating gate by programming or erasing, respectively.

[0007] It is the primary object of the present invention to provide Eprom and EEprom cell and array structures and processes for making them that result in cells of reduced size so their density on a semiconductor chip can be increased. It is also an object of the invention that the structures be highly manufacturable, reliable, scalable, repeatable and producible with a very high yield.

[0008] It is yet another object of the present invention to provide EEprom semiconductor chips that are useful for solid state memory to replace magnetic disk storage devices.

[0009] Another object of the present invention is to provide a technique for increasing the amount of information that can be stored in a given size Eprom or EEprom array.

[0010] Further, it is an object of the present invention to provide a technique for increasing the number of program/read cycles that an EEprom can endure.

SUMMARY OF THE INVENTION

[0011] These and additional objects are accomplished by the various aspects of the present invention, either alone or in combination, the primary aspects being briefly summarized as below:

[0012] 1. The problems associated with prior art split channel Eprom and split channel Flash EEprom devices are overcome by providing a split channel memory cell constructed in one of the following ways:

[0013] (A) In one embodiment, one edge of the floating gate is self aligned to and overlaps the edge of the drain diffusion and the second edge of the floating gate is self aligned to but is spaced apart from the edge of the source diffusion. A sidewall spacer formed along the second edge of the floating gate facing the source side is used to define the degree of spacing between the two edges. Self alignment of both source and drain to the edges of the floating gate results in a split channel Eprom device having accurate control of the three most critical device parameters: Channel segment lengths **L1** and **L2** control-lable by floating gate and control

gate, respectively, and the extent of overlap between the floating gate and the drain diffusion. All three parameters are insensitive to mask misalignment and can be made reproducibly very small in scaled-down devices.

[0014] (B) In a second embodiment of the split channel Eprom a heavily doped portion of the channel adjacent to the drain diffusion is formed by a novel, well-controlled technique. The length Lp and doping concentration of this channel portion become the dominant parameters for programming and reading, thereby permitting the formation of a split channel structure which is relatively insensitive to misalignments between the floating gate and the source/drain regions.

[0015] 2. A separate erase gate is provided to transform a Eprom device into a Flash EEprom device. The area of overlap between the floating gate and the erase gate is insensitive to mask misalignment and can therefore be made reproducibly very small.

[0016] 3. In some embodiments of this invention, the erase gate is also used as a field plate to provide very compact electric isolation between adjacent cells in a memory array.

[0017] 4. A new erase mechanism is provided which employs tailoring of the edges of a very thin floating gate so as to enhance their effectiveness as electron injectors.

[0018] 5. A novel intelligent programming and sensing technique is provided which permits the practical implementation of multiple state storage wherein each Eprom or flash EEprom cell stores more than one bit per cell.

[0019] 6. A novel intelligent erase algorithm is provided which results in a significant reduction in the electrical stress experienced by the erase tunnel dielectric and results in much higher endurance to program/erase cycling.

[0020] The combination of various of these features results in new split channel Eprom or split channel Flash EEprom devices which are highly manufacturable, highly scalable, and offering greater storage density as well as greater reliability than any prior art Eprom or Flash EEprom devices. Memories that utilize the various aspects of this invention are especially useful in computer systems to replace existing magnetic storage media (hard disks and floppy disks), primarily because of the very high density of information that may be stored in them.

[0021] Additional objects, features and advantages of the present invention will be understood from the following description of its preferred embodiments, which description should be taken in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0022] **FIG. 1** is a cross section of the split channel Flash EEprom Samachisa prior art cell which erases by tunneling of electrons from the floating gate to the drain diffusion.

[0023] **FIG. 2***a* is a cross section of the Flash EEprom Kynett prior art cell which erases by tunneling of electrons from the floating gate to the source diffusion.

[0024] **FIG. 2***b* is a cross section of the Flash EEprom Kupec prior art cell with triple polysilicon.

[0025] **FIG. 2***c* is a schematic of the Kupec cell during erase.

[0026] **FIG. 3***a* is a topological view of the triple polysilicon split channel Flash EEprom prior art Masuoka cell which erases by tunneling of electrons from the floating gate to an erase gate.

[0027] **FIG. 3***b* is a schematic view of the Masuoka prior art cell of **FIG. 3***a*.

[0028] **FIG. 3***c* is a view of the Masuoka prior art cell of **FIG. 3***a* along cross section AA.

[0029] **FIG. 3***d* is a cross section view of the split channel Eprom Harari prior art cell.

[0030] **FIG. 4***a* is a cross section view of the split channel Eprom Eitan prior art cell having a drain diffusion self aligned to one edge of the floating gate.

[0031] **FIG. 4***b* is a cross section view of the prior art Eitan cell of **FIG. 4***a* during the process step used in the formation of the self aligned drain diffusion.

[0032] **FIG. 4***c* is a cross section view of the split channel Eprom Mizutani prior cell with sidewall spacer forming the floating gate.

[0033] **FIG. 4***d* is a cross section view of the split channel Eprom Wu prior art cell with sidewall spacer forming one of two floating gates.

[0034] **FIG. 4***e* is a cross section view of a stacked gate Eprom Tanaka prior art cell with heavily doped channel adjacent to the drain junction.

[0035] **FIG. 5***a* is a cross section of a split channel Eprom cell in accordance with this invention.

[0036] **FIG. 5***b* through **5***f* are cross sections of the cell of **FIG. 5***a* during various stages in the manufacturing process.

[0037] **FIG. 6***a* is a top view of a 2×2 array of Flash EEprom cells formed in a triple layer structure in accordance with one embodiment of this invention.

[0038] **FIG. 6***b* is a view along cross section AA of the structure of **FIG. 6***a*.

[0039] **FIG. 7***a* is a top view of a 2×2 array of Flash EEprom cells formed in a triple layer structure in accordance with a second embodiment of this invention wherein the erase gates also provide field plate isolation.

[0040] **FIG. 7***b* is a view along cross section AA of the structure of **FIG. 7***a*.

[0041] **FIG. 7***c* is a view along cross section CC of the structure of **FIG. 7***a*.

[0042] **FIG. 8***a* is a top view of a 2×2 array of Flash EEprom cells formed in a triple layer structure in accordance with a third embodiment of this invention wherein the tunnel erase dielectric is confined to the vertical surfaces at the two edges of the floating gate.

[0043] **FIG. 8***b* is a view along cross section AA of the structure of **FIG. 8***a*.

[0044] **FIG. 9***a* is a top view of a 2×2 array of Flash EEprom cells formed in a triple layer structure in accordance

with a fourth embodiment of this invention wherein the erase gate is sandwiched in between the floating gate and the control gate.

[**0045**] **FIG. 9***b* is a view along cross section AA of the structure of **FIG. 9***a*.

[**0046**] **FIG. 9***c* is a view along cross section DD of the structure of **FIG. 9***a*.

[**0047**] **FIG. 10** is a schematic representation of the coupling capacitances associated with the floatings gate of the Flash EEprom cell of the invention.

[**0048**] **FIG. 11***a* is a schematic representation of the composite transistor forming a split channel Eprom device.

[**0049**] **FIG. 11***b* shows the programming and erase characteristics of a split channel Flash EEprom device.

[**0050**] **FIG. 11***c* shows the four conduction states of a split channel Flash EEprom device in accordance with this invention.

[**0051**] **FIG. 11***d* shows the program/erase cycling endurance characteristics of prior art Flash EEprom devices.

[**0052**] **FIG. 11***e* shows a circuit schematic and programming/read voltage pulses required to implement multistate storage.

[**0053**] **FIG. 12** outlines the key steps in the new algorithm used to erase with a minimum stress.

[**0054**] **FIG. 13** shows the program/erase cycling endurance characteristics of the split channel Flash EEprom device of this invention using intelligent algorithms for multistate programming and for reduced stress during erasing.

[**0055**] **FIGS. 14***a*, **14***b* and **14***c* are cross sections of another embodiment of this invention during critical steps in the manufacturing flow.

[**0056**] **FIGS. 15***a* and **15***b* are schematic representations of two memory arrays for the Flash EEprom embodiments of this invention.

[**0057**] **FIGS. 16***a* and **16***b* are cross sectional views of Flash EEprom transistors, illustrating the erase mechanism by asperity injection (**16***a*) and sharp tip injection (**16***b*).

[**0058**] **FIGS. 16***c* and **16***d* are cross sectional views of parts of Flash EEprom transistors illustrating the formation of sharp-tipped edges of the floating gate by directional etching to facilitate high field electronic injection.

[**0059**] **FIG. 17***a* contains Table I which shows voltage conditions for all operational modes for the array of **FIG. 15***a*.

[**0060**] **FIG. 17***b* contains Table II which shows example voltage conditions for all operational modes for the virtual ground array of **FIG. 15***b*.

DETAILED DESCRIPTION OF THE PRIOR ART

[**0061**] There are two distinctly different approaches in the prior art of Flash EEproms. A triple polysilicon device was described by J. Kupec et al. in 1980 *IEDM Technical Digest*, p. 602 in an article entitled "Triple Level Polysilicon EEprom with Single Transistor per Bit". An improvement to the Kupec device was proposed by F. Masuoka and H. Iizuka in U.S. Pat. No. 4,531,203, issued Jul. 23, 1985. Variations on the same cell are described by C. K. Kuo and S. C. Tsaur in U.S. Pat. No. 4,561,004 issued Dec. 24, 1985, and by F. Masuoka et al. in an article titled "A 256K Flash EEprom Using Triple Polysilicon Technology", *Digest of Technical Papers, IEEE International Solid-State Circuits Conference*, February 1985, p. 168.

[**0062**] The second approach is a double polysilicon cell described by G. Samachisa et al., in an article titled "A 128K Flash EEprom Using Double Polysilicon Technology", *IEEE Journal of Solid State Circuits*, October 1987, Vol. SC-22, No. 5, p. 676. Variations on this second cell are also described by H. Kume et al. in an article titled "A Flash-Erase EEprom Cell with an Asymmetric Source and Drain Structure", *Technical Digest of the IEEE International Electron Devices Meeting*, December 1987, p. 560, and by V. N. Kynett et al. in an article titled "An In-System Reprogrammable 256K CMOS Flash Memory", *Digest of Technical Papers, IEEE International Solid-State Circuits Conference*, February 1988, p. 132. A cross-section of the Samachisa cell is shown in **FIG. 1**. Transistor **100** is an NMOS transistor with source **101**, drain **102**, substrate **103**, floating gate **104** and control gate **109**. The transistor has a split channel consisting of a section **112** (L1) whose conductivity is controlled by floating gate **104**, in series with a section **120** (L2) whose conductivity is controlled by control gate **109**. Programming takes place as in other Eprom cells by injection of hot electrons **107** from the channel at the pinchoff region **119** near the drain junction. Injected electrons are trapped on floating gate **104** and raise the conduction threshold voltage of channel region **112** and therefore of transistor **100**. To erase transistor **100** the oxide in region **112** separating between the floating gate **104** and drain diffusion **102** and channel **112** is thinned to between 15 and 20 nanometers, to allow electronic tunneling of trapped electrons **108** from the floating gate to the drain. In the Samachisa cell the appropriate voltages applied to achieve programming are V_{CG}=12V, V_D=9V, V_{BB}=0V, V_S=0V, and to achieve erase are V_{CG}=OV, V_D=19V, V_{BB}=OV, V_S=floating. Samachisa points out that the electrical erase is not self-limiting. It is possible to overerase the cell, leaving the floating gate positively charged, thus turning the channel portion L1 into a depletion mode transistor. The series enhancement transistor L2 is needed therefore to prevent transistor leakage in the overerase condition.

[**0063**] The Samachisa cell suffers from certain disadvantages. These are:

[**0064**] (a) It is difficult to prevent avalanche junction breakdown or high junction leakage current at the drain junction **102** during the time the very high erase voltage is applied to the drain;

[**0065**] (b) It is difficult to-grow with high yields the thin oxide layer **112** used for tunnel erase;

[**0066**] (c) Because of the presence of thin oxide layer between the floating gate and the drain diffusion, it is difficult to prevent accidental tunneling of electrons from the floating gate to the drain in what is known as the "program disturb" condition. Under this condition an unselected cell in a memory array sharing the same drain (bit line) as a programmed cell may have a drain voltage of approximately 10 volts and a control gate voltage of 0 volts. Although this represents a much weaker electric field than that experienced

during tunnel erase (when the drain is at approximately 19 volts), it nevertheless can, over a prolonged period of time alter by slow tunneling the charge stored on the floating gate.

[0067] The Kynett and Kume cells (**FIG. 2***a*) are similar to the Samachisa cell except for the elimination of the series enhancement transistor **120**, and the performing of tunnel erase **208** over the source diffusion **201** rather than over the drain diffusion **202**. Typically the Kynett cell uses during programming voltages V_{CG}=12V, V_D=8V, V_S=0V, V_{BB}=0V, and during erase voltages V_S=12V, V_{BB}=OV, V_{CG}=OV, V_D=Floating. Kynett achieves a lower erase voltage than Samachisa by thinning tunnel dielectric **212** to 10 nanometers or less, so that even though the voltage applied to the source diffusion during erase is reduced, the electric field across tunnel dielectric **212** remains as high as in the case of the Samachisa cell.

[0068] The Kynett cell can be contrasted with the Samachisa cell:

[0069] (a) Kynett is less susceptible to avalanche breakdown of source diffusion **201** during erase because the voltage is reduced from 19 volts to 12 volts.

[0070] (b) Kynett's cell is more susceptible to low yields due to pinholes in the thin dielectric layer **212** because its thickness is reduced from approximately 20 nanometers to approximately 10 nanometers.

[0071] (c) Because Kynett uses a lower voltage for erase but essentially the same drain voltage for programming Kynett is far more susceptible to accidental "program disturb" due to partial tunnel erase (during programming) occuring from floating gate **204** to drain **202**.

[0072] (d) Kynett's cell is highly susceptible to an overerase condition because it does not have the series enhancement channel portion **120** of Samachisa's cell. To prevent overerase Kynett et al. deploy a special erase algorithm. This algorithm applies a short erase pulse to an array of cells, then measures the threshold voltage of all cells to ensure that no cell has been overetased into depletion. It then applies a second erase pulse and repeats the reading of all cells in the array. This cycle is stopped as soon as the last cell in the array has been erased to a reference enhancement voltage threshold level. The problem with this approach is that the first cell to have been adequately erased continues to receive erase pulses until the last cell has been adequately erased, and may therefore be susceptible to overerase into a depletion threshold state.

[0073] Kupec's cell employs essentially the Kynett cell without a thin tunnel dielectric over the source, channel, or drain, and with a third polysilicon plate covering the entire transistor and acting as an erase plate. A cross sectional view of the Kupec device is shown in **FIG. 2***b*. Transistor **200***b* consists of a stacked floating gate **204***b* and control gate **209***b* with source **201***b* and drain **202***b* self aligned to the edges of the floating gate. Gate dielectric **212** is relatively thick and does not permit tunnel erase from floatina gate to source or drain. An erase plate **230***b* overlies the control gate and covers the sidewalls of both the control gate and the floating gate. Erase takes place by tunneling across the relatively thick oxide **231***b* between the edges of floating gate **204***b* and erase plate **230***b*. Kupec attempts to overcome the overerase condition by connecting the erase plate during high voltage erase to drain **202***b* and through a high impedance resistor R (**FIG. 2***c*) to the erase supply voltage V_{ERASE}. As soon as the cell is erased into depletion the drain to source transistor conduction current drops most of the erase voltage across the resistor, reducing the voltage on the erase plate **230***b* to below the tunneling voltage. This approach is extremely difficult to implement in a block erase of a large array because different transistors begin conduction at different times.

[0074] Masuoka's approach to Flash EEprom overcomes most of the disadvantages of the Samachisa, Kynett and Kupec cells. **FIG. 3***a* provides a top view of the Masuoka prior art cell, **FIG. 3***b* shows the schematic representation of the same cell, and **FIG. 3***c* provides a cross section view along the channel from source to drain. Transistor **300** consists of a split channel Eprom transistor having a source **301**, a drain **302**, a floating gate **304** controlling channel conduction along section L1 (**312**) of the channel, a control gate **309** capacitively coupled to the floating gate and also controlling the conduction along the series portion of the channel L2 (**320**), which has enhancement threshold voltage.

[0075] The transistor channel width (W), as well as the edges of the source and drain diffusions are defined by the edges **305** of a thick field oxide formed by isoplanar oxidation. Oxide **332** of thickness in the 25 to 40 nanometers range is used as isolation between the floating gate and the substrate. Masuoka adds an erase gate **330** disposed underneath the floating gate along one of its edges. This erase gate is used to electrically erase floating gate **304** in an area of tunnel dielectric **331** where the floating gate overlaps the erase gate. Tunnel dielectric **331** is of thickness between 30 and 60 nanometers.

[0076] Masuoka specifies the following voltages during erase: V_S=OV, V_D=OV, V_{CG}=OV, V_{BB}=OV, V_{ERASE}=20V to 30V.

[0077] Comparing the Masuoka cell with the Samachisa and Kynett cells:

[0078] (a) Masuoka's cell does not erase by using either the source diffusion or the drain diffusion for tunnel erase. Therefore these diffusions never experience a voltage higher than during Eprom programming. The junction avalanche breakdown and junction leakage problems therefore do not exist.

[0079] (b) Masuoka's cell uses a relatively thick tunnel dielectric and therefore does not need to use thin tunnel dielectrics for erase. Therefore it is less susceptible to oxide pinholes introduced during the manufacturing cycle.

[0080] (c) Masuoka's cell does not have a "program disturb" problem because programming and tunnel erase involve two different mechanisms occuring at two different regions of the transistor.

[0081] (d) Masuoka's cell is not susceptible to the overerase condition because of the presence of the series enhancement transistor channel **320** (L2).

[0082] (e) Masuoka's cell requires a third layer of polysilicon, which complicates the process as well as aggravates the surface topology. Because the erase gate consumes surface area over the field oxide **305** it results in a larger cell.

[0083] (f) The overlap area **331** in Masuoka's cell is sensitive to mask misalignment between the two masks

defining this overlap. Since the overlap area is nominally very small, even small misalignments can result in large variations in the area used for tunnel erase. This results in severe variations from wafer to wafer.

[**0084**] From the foregoing analysis it is clear that while the Masuoka prior art cell successfully addresses most of the problems encountered by Samachisa and Kynett, it itself has disadvantages not encountered by Samachisa or Kynett.

[**0085**] Masuoka and Samachisa both use a split channel Eprom transistor for programming. In the split channel eprom transistor, the portion L2 of the channel length controlled by control gate **109**, **309** has a fixed enhancement threshold voltage determined by the p+ channel doping concentration **360**. The portion L1 of the channel length controlled by floating gate **104** (Samachisa) and **304** (Masuoka) has a variable threshold voltage determined by the net charge stored on the floating gate.

[**0086**] Other prior art split channel Eprom transistors are described by E. Harari in U.S. Pat. No. 4,328,565, May 4, 1982 and by B. Eitan in U.S. Pat. No. 4,639,893, Jan. 27, 1987. The Harari split channel Eprom transistor **300***d* is shown in cross section in **FIG. 3***d*. Source **301***d* and drain **302***d* are formed prior to formation of the floating gate **304***d*. Therefore, the total channel length L1+L2 is insensitive to mask misalignment. However, both L1 and L2 are sensitive to misalignment between floating gate **304***d* and drain diffusion **302***d*.

[**0087**] The Eitan split channel Eprom transistor **400** is shown in cross sections in **FIG. 4***a*. The Eitan patent highlights the main reasons for using a split channel architecture rather than the standard self aligned stacked gate Eprom transistor **200** (FIG. 2). These reasons can be summarized as follows:

[**0088**] The addition of a fixed threshold enhancement transistor in series with the floating gate transistor decouples the floating gate from the source diffusion. This allows the channel length L1 to be made very small without encountering punchthrough between source and drain. Furthermore, transistor drain-turnon due to the parasitic capacitive coupling between the drain diffusion and the floating gate is eliminated because the enhancement channel portion L2 remains off.

[**0089**] Eitan shows that the shorter the length L1 the greater the programming efficiency and the greater the read current of the split channel Eprom transistor. For Flash EEprom devices the series enhancement channel L2 acquires additional importance because it allows the floating gate portion L1 to be overerased into depletion thereshold voltage without turning on the composite split channel transistor.

[**0090**] The disadvantages incurred by the addition of the series enhancement channel L2 are an increase in cell area, a decrease in transistor transconductance, an increase in control gate capacitance, and an increase in variability of device characteristics for programming and reading brought about by the fact that L1 or L2 or both are not precisely controlled in the manufacturing process of the prior art split channel devices. Samachisa, Masuoka and Eitan each adopt a different approach to reduce the variability of L1 and L2:

[**0091**] Samachisa's transistor **100** (**FIG. 1**) uses the two edges **140**, **143** of control gate **109** to define (by a self aligned ion implant) drain diffusion **102** and source diffusion **101**. Edge **141** of floating gate **104** is etched prior to ion implant, using edge **140** of control gate **109** as an etch mask. This results in a split channel transistor where (L1+L2) is accurately controlled by the length between the two edges **140**, **143** of the control gate. However, L1 and L2 are both sensitive to misalignment between the mask defining edge **142** and the mask defining edges **140**, **143**.

[**0092**] Masuoka's transistor **300** (**FIG. 3***c*) forms both edges **341**, **342** of floating gate **304** in a single masking step. Therefore L1 is insensitive to mask misalignment. L2, which is formed by ion implant of source diffusion **301** to be self aligned to edge **343** of control gate **309**, is sensitive to misalignment between the mask defining edge **342** and the mask defining edge **343**. Furthermore the Masuoka transistor **300** may. form a third channel region, L3, if edge **340** of control gate **309** is misaligned in a direction away from edge **341** of floating gate **304**. the formation of L3 will severely degrade the programming efficiency of such a cell.

[**0093**] Eitan's transistor **400** (**FIGS. 4***a*, **4***b*) uses a separate mask layer **480** to expose the edge of floating gate **404** to allow drain diffusion **402** to be self aligned (by ion implantation) to edge **441** of floating gate **404**. Therefore L1 can be accurately controlled and is not sensitive to mask misalignment. L2 however is sensitive to the misalignment between edge **482** of photoresist **480** and edge **442** of the floating gate. Eitan claims that the variability in L2 due to this mask misalignment, can be as much as 1.0 micron or more without affecting the performance of the device (see claims 3, 4 of the above-referenced Eitan patent).

[**0094**] It should be pointed out that even with the most advanced optical lithography systems available today in a production environment it is difficult to achieve an alignment accuracy of better than ±0.25 microns between any two mask. layers. Therefore the variability in L2 or L1 inherent to any structure which is alignment sensitive can be as much as approximately 0.5 microns from one extreme to the other.

[**0095**] Another prior art split channel Eprom device which attempts to achieve the objective of accurately establishing L1 and L2 is disclosed by Y. Mizutani and K. Makita in the 1985 *IEDM Technical Digest*, p. 63, shown in cross section in **FIG. 4***c*. Transistor **400***c* has a floating gate **404***c* formed along the sidewall **440***c* of control gate **409***c*. In this way both L1 and L2 can be independently established and are not sensitive to mask misalignment. Transistor **400***c* has the drawback that the capacitive coupling between control gate **409***c* and floating gate **404***c* is limited to the capacitor area of the sidewall shared between them, which is relatively a small area. Therefore there is a very weak capacitive coupling between the control gate and the floating gate either during programming or during read. Therefore, although the device achieves good control of L1 and L2 it is of rather low efficiency for both modes of operation.

[**0096**] Yet another prior art device which has a split channel with a well controlled L1 and L2 is disclosed by A. T. Wu et al. in the 1986 *IEDM Technical Digest*, p. 584 in an article entitled "A Novel High-Speed, 5-Volt Programming Eprom Structure with Source-Side Injection". A cross section of the Wu prior art transistor is shown in **FIG. 4***d* (FIG. 2 in the above-referenced article). This transistor has a floating gate **404***d* coupled to a control gate **409***d*, extending over channel region L1 (**412***d*), in series with a second

floating gate **492***d* formed in a sidewall adjacent to source diffusion **401***d* and overlying channel region L2 (**420***d*). This second floating gate is capacitively coupled to the control gate **409***d* through the relatively small area of the sidewall **493***d* shared between them and is therefore only marginally better than the Mizutani prior art device, although it does achieve a good control of both L1 and L2.

[**0097**] Another prior art Eprom transistor which does not have a split channel structure but which seeks to achieve two distinct channel regions to optimize the Eprom programming performance is disclosed by S. Tanaka et al. in 1984 *ISSCC Digest of Technical Papers*, p. 148 in an article entitled "A Programmable 256K CMOS Eprom with On Chip Test Circuits". A cross section of this device is shown in **FIG. 4***e* (corresponding to FIG. 3 in the Tanaka article). Transistor **400***e* is a stacked gate Eprom transistor (not split channel) with source **401***e* and drain **402***e* self aligned to both edges of floating gate **404***e* and control gate **409***e*. The channel region is more heavily p doped **460***e* than the p substrate **463***e*, but in addition there is a second p+ region **477***e* which is even more heavily p-doped than region **460***e*. This region **477***e* is formed by diffusion of boron down and sideways from the top surface on the drain side only, and is formed after formation of the floating gate so as to be self aligned to the floating gate on the drain side. The extent of sideway diffusion of boron ahead of the sideway diffusion of arsenic from the N+ drain junction defines a channel region Lp (**478***e*) adjacent to the drain. This is a DMOS type structure, called DSA (Diffusion Self Aligned) by Tanaka. The presence of the p+ region **478***e* reduces considerably the width of the drain depletion region during high voltage programming. A shorter depletion layer width results in greater energy being imparted to channel electrons entering the depletion region, which in turn results in significant increase in programming efficiency through hot electron injection. Transistor **400***e* has proven difficult to manufacture because it is rather difficult to control the length Lp and the surface channel concentration p+ through a double diffusion step. Furthermore, it is rather difficult to obtain value of Lp bigger than approximately 0.3 microns by diffusion because device scaling dictates the use of rather low temperature diffusion cycles. Still further, the DSA Eprom device suffers from an excessively high transistor threshold voltage in the unprogrammed (conducting) state, as well as from high drain junction capacitance. Both these effects can increase substantially the read access time.

Detailed Description of Specific Embodiments of the Invention

[**0098**] I.a. Split Channel Eprom Transistor with Self Aligned Drain Diffusion and Self Aligned Spaced Apart Source Diffusion

[**0099**] **FIG. 5***a* presents a cross sectional view of a split channel Eprom transistor in accordance with. a first embodiment of this invention. Transistor **500***a* consists of a p type silicon substrate **563** (which can alternatively be a p type epitaxial layer grown on top of a p++ doped silicon substrate), N+ source diffusion **501***a*, N+ drain diffusion **502***a*, a channel region **560***a* which is more heavily p-doped than the surrounding substrate, a floating gate **504***a* overlying a portion L1 of the channel, **512***a*, and a control gate **509** overlying the remaining portion L2 of the channel, **520***a* as well as the floating gate. Floating gate **504***a* is dielectrically isolated from the surface of the silicon substrate by dielectric film **564***a*, which is thermally grown Silicon Dioxide. Control gate **509** is capacitively coupled to floating gate **504***a* through dielectric film **567***a*, which can either be thermally grown Silicon Dioxide or a combination of thin layers of Silicon Dioxide and Silicon Nitride. Control gate **509** is also insulated from the silicon surface in channel portion L2 as well as over the source and drain diffusions by dielectric film **565***a*, which is made of the same material as dielectric **567***a*.

[**0100**] P-type substrate **563** is typically 5 to 50 Ohms centimeter, p+ channel doping **560***a* is typically in the range of 1×10^{16} cm^{-3} to 2×10^{17} cm^{-3}, dielectric film **564***a* is typically 20 to 40 nanometers thick, dielectric film **567***a* is typically 20 to 50 nanometers thick, floating gate **504***a* is usually a heavily N+ doped film of polysilicon of thickness which can be as low as 25 nanometers (this thickness will be discussed in Section VII) or as high as 400 nanometers. Control gate **509** is either a heavily N+ doped film of polysilicon or a low resistivity interconnect material such as a silicide or a refractory metal. Of importance, edge **523***a* of N+ drain diffusion **502***a* formed by ion implantation of Arsenic or Phosphorus is self aligned to edge **522***a* of floating gate **504***a*, while edge **521***a* of N+ source diffusion **501***a* formed by the same ion implantation step is self aligned to, but is spaced apart from, edge **550***a* of the same floating gate **504***a*, using a sidewall spacer (not shown in **FIG. 5***a*) which is removed after the ion implantation but prior to formation of control gate **509**. The implant dose used to form diffusions **501***a*, **502***a*, is typically in the range of 1×10^{15} cm^{-2} to 1×10^{16} cm^{-2}.

[**0101**] The key steps for the formation of channel portions L1 and L2 are illustrated in **FIGS. 5***b* through **5***f*. In the structure of **FIG. 5***b* floating gates **504***a*, **504***b* are formed in a layer of N+ doped polysilicon on top of a thin gate oxide **564***a*, by anisotropic reactive ion etchings, using photoresist layer **590** as a mask. In **FIG. 5***c* a thin protective film **566***a* is deposited or thermally grown, followed by the deposition of a thick spacer layer **570**. The purpose of film **566***a* is to protect the underlying structure such as layer **565***a* from being etched or attacked when the spacer film is etched back. The spacer film is now etched back in an anisotropic reaction ion etch step with carefully controlled timing. The conditions for etchback must have no significant undercutting and must have a differential etch rate of 20:1 or higher between the spacer material and the material of protective film **566***a*. Spacer layer **570** can be a conformal film of undoped LPCVD polysilicon while protective film **566***a* can be silicon dioxide or silicon nitride. Alternatively, spacer layer **570** can be a conformal film of LPCVD silicon dioxide while protective film **566***a* can be either LPCVD silicon nitride or LPCVD polysilicon. The thickness of protective film **566***a* should be as thin as possible, typically in the range of 10 to 30 nanometers, so as to to allow penetration of the subsequent Arsenic implantation to form the source and drain diffusions.

[**0102**] The thickness of the conformal spacer layer determines the width of the sidewall spacer, and therefore also the length of channel portion L2. Typically for an L2 of 400 nanometers a spacer layer of approximately 600 nanometers thickness is used.

[**0103**] In **FIG. 5***d* spacers **592***a*, **593***a* and **592***b*, **593***b* are formed along the vertical edges of floating gates **504***a* and

504*b* respectively at the completion of the timed reactive ion etch step. These spacers result from the fact that the thickness of layer **570** is greater adjacent to the vertical walls of the floating gates than it is on flat surfaces. Therefore a carefully timed anisotropic reactive ion etchback will etch through layer **570** in areas of flat surface topology while not completely etching through it along each edge, forming the spacers. The technique for formation of narrow sidewall spacers along both edges of the gate of MOS transistors is well known in the industry, and is commonly used to form lightly doped drains (LDD) in short channel MOSFETS. (See, for example, FIG. 1 in an article in 1984 *IEDM Technical Digest*, p. 59 by S. Meguro et al. titled "Hi-CMOS III Technology".)

[**0104**] In the present invention, the spacer can be significantly wider, it is used along one edge only, and it is used not to define a lightly doped source or drain but rather to define the series enhancement transistor channel portion L2.

[**0105**] The next step is a masking step. Photoresist **591***a*, **591***b* (**FIG. 5***d*) is used as a mask to protect spacers **592***a*, **592***b* while exposing spacers **593***a*, **593***b*. The latter are etched away, preferably with a wet chemical etch (which should be chosen so as to not etch protective film **566***a*), and the photoresist is stripped.

[**0106**] In **FIG. 5***e* ion implantation of Arsenic through dielectric films **566***a* and **565***a* is used to form N+ source diffusions **501***a*, **501***b* and N+ drain diffusions **502***a*, **502***b*. On the drain side these diffusions are self aligned to edges **522***a* and **522***b* of the floating gates. On the source side the diffusions are self aligned to edges **550***a* and **550***b* of the floating gates but are spaced apart from these edges by the width of spacers **592***a* and **592***b* less the sideways diffusion in subsequent high temperature process steps.

[**0107**] Next, spacers **592***a*, **592***b* and the protective film **566***a* are removed (**FIG. 5***f*), preferably with wet etches which will not attack the underlying layers **565***a* and **504***a*. Dielectric film **567***a* is grown by thermal oxidation or deposited by LPCVD on the exposed surfaces of the floating gates and substrate. A conductive layer is then deposited and control gates **509***a*, **509***b* are formed through etching of long narrow strips which constitute the word lines in rows of memory cells in an array.

[**0108**] The remaining part of the process is standard:

[**0109**] The surface of the structure is covered with a thick passivation layer **568**, usually phosphorous doped glass or a Borophosphosilicate glass (BPSG). This passivation is made to flow in a high temperature anneal step. Contact vias are etched (not shown in **FIG. 5***f*) to allow electrical access to the source and drain diffusions. Metallic interconnect strips **569***a*, **569***b* are provided on top of passivation layer **568**, accessing the source and drain diffusions through the via openings (not shown).

[**0110**] Comparing split channel transistor **500***a* of **FIG. 5***f* with the Samachisa, Masuoka, Harari and Eitan prior art split channel transistors **100**, **300**, **300***d* and **400**, the advantages of transistor **500***a* can be summarized as follows:

[**0111**] a) L1 and L2 are insensitive to mark misalignment. Therefore they can be controlled much more accurately and reproducibly than the prior art.

[**0112**] b) Because all four prior art transistors **100**, **300**, **300***d* and **400** define L2 through a mask alignment tolerance whereas transistor **500***a* defines L2 through control of the width of a sidewall spacer it is possible in transistor **500***a* to achieve controllably a much shorter channel portion L2 than possible through a mask alignment. This becomes an important consideration in highly scaled split channel Eprom and Flash EEprom transistors.

[**0113**] I.b. Split Channel Eprom Transistor with Heavily Doped Channel Adjacent to the Drain Junction

[**0114**] **FIG. 14***c* presents a cross sectional view of a non self aligned split channel Eprom transistor in accordance with a second embodiment of this invention. **FIGS. 14***a* and **14***b* illustrate the critical process steps in the manufacturing process of this device. Transistor **1400** consists of a p type silicon substrate **1463** (which can also be a p type epitaxial layer grown on a p++ substrate). Shallow N+ source diffusions **1401** and N+ drain diffusions **1402** are formed prior to formation of floating gate **1404**, in contrast with the embodiment of section Ia above. The channel region between the source and drain diffusions is split into two portions: a portion L1 (**1412**) which is lying directly underneath the floating gate, and a portion L2 (**1420**) which is lying directly underneath the control gate **1409**. The improvement over the Harari prior art split channel transistor **300***d* (**FIG. 3***d*) consists of a heavily p+ doped narrow region **1460** adjacent to drain diffusion **1402**. The width Lp (**1413**) and doping concentration of this region at the top surface where the field effect transistor. channel is formed, become the controlling parameters for device programming and reading efficiency, provided that p+ is sufficiently high. Typically, p substrate **1463** may have a p type doping concentration of 1×10^{16} cm^{-3} whereas p+ region **1460** may have a p+ type doping concentration of between 1×10^{17} cm^{-3} and 1×10^{18} cm^{-3}. In the preferred manufacturing process the length Lp and doping concentration of region **1460** are chosen so that the depletion region width at the drain junction under programming voltage conditions is less than the width Lp. So long as that condition is satisfied, and so long as L1 is bigger than Lp, then the actual value of L1 is of secondary importance to the device performance. Since L1 in this device is determined through a mask alignment between the floating gate and the drain it is not as well controlled as in the Eitan prior art transistor **400**. However, to the extent that region **1460** can be made to be self aligned to the drain so that parameter Lp is not sensitive to mask alignment, then any variability in L1 is of secondary importance, Lp being the controlling parameter.

[**0115**] A new method is disclosed for manufacturing the split channel Eprom transistor **1400** which results in much better control of the parameter Lp and of the surface channel doping concentration **1413** than is provided by the DSA (Diffusion Self Align) approach of the Tanaka prior art transistor **400***e* (**FIG. 4***e*).

[**0116**] The main steps in this new method for the fabrication of a memory array of transistors **1400** are as follows:

[**0117**] 1. In the structure of **FIG. 14***a* a thin oxide layer **1475**, typically **50** nanometers of silicon dioxide, is covered with a layer **1474** of silicon nitride, approximately 100 nanometers thick. This in turn is covered with a second layer **1473** of deposited silicon dioxide, approximately 100

nanometers thick. Oxide **1475** and nitride **1474** can, for example, be the same films used to form isoplanar isolation regions in the periphery of the memory array.

[**0118**] 2. A photoresist mask P.R.**1** (**1470**) is used to define source and drain regions in long parallel strips extending in width between edges **1471**, **1472** of openings in the photoresist. Exposed oxide layer **1473** is now wet etched in a carefully controlled and timed etch step which includes substantial undercutting of photoresist **1470**. The extent of undercutting, which is measured by the distance Lx between oxide edges **1476** and **1478**, will eventually determine the magnitude of parameter Lp. Typically, Lx is chosen between 300 nanometers and 700 nanometers. The three parameters critical for a reproducible Lx are the concentration and temperature of the etch solution (hydrofluoric acid) and the density (i.e., lack of porosity) of the oxide **1473** being etched. These can be well controlled sufficiently so that a timed undercutting etch step results in well controlled etched strips of width Lx and running parallel to edges **1471**, **1472** of the long openings in the photoresist. In fact, for values of Lx below approximately 500 nanometers, it is easier to achieve a reproducible Lx through controlled sideway etching than by controlling the line width of long, narrow line in a photoresist layer. An example of the use of sideway etching self aligned to an edge in a similar fashion (but to achieve the different purpose of forming a very narrow guard ring) can be found in the prior art article by S. Kim titled "A Very Small Schottky Barrier Diode with Self-Aligned Guard Ring for VLSI Application", appearing in the 1979 *IEDM Technical Digest*, p. 49.

[**0119**] 3. At the completion of the sideway etch step a second, anisotropic etch is performed, using the same photoresist mask P.R.**1** to etch away long strips of the exposed silicon nitride film **1474**. Edges **1471**, **1472** of P.R.**1** (**1470**) are used to form edges **1480**, **1481** respectively in the etched strips of nitride layers.

[**0120**] 4. Arsenic ion implantation with an ion dose of approximately 5×10^{15} cm^{-2} is performed with an energy sufficient to penetrate oxide film **1475** and dope the surface in long strips of N+ doped regions (**1402**, **1401**). Photoresist mask P.R.**1** can be used as the mask for this step, but nitride layer **1474** can serve equally well as the implant mask. P.R.**1** is stripped at the completion of this step.

[**0121**] 5. An implant damage anneal and surface oxidation step follows, resulting in 200 to 300 nanometers of silicon dioxide **1462** grown over the source and drain diffusion strips. The temperature for this oxidation should be below 1000° C. to minimize the lateral diffusion of the N+ dopants in regions **1402**, **1401**. If desired it is possible through an extra masking step to remove nitride layer **1474** also from the field regions between adjacent channels, so as to grow oxide film **1462** not only over the source and drain regions but also over the field isolation regions.

[**0122**] 6. In **FIG. 14***b* a second photoresist mask P.R.**2** (**1482**) is used to protect the source-side (**1401**) of the substrate during the subsequent implant step. This implant of boron can be performed at relatively high energy sufficient to penetrate through nitride layer **1474** and oxide layer **1475** but not high enough to penetrate top oxide **1473**, nitride **1474** and oxide **1475**. Alternatively, nitride layer **1474** can first be etched along edge **1482**, using edge **1478** of the top oxide **1473** as a mask. The boron implant dose is in the range of 1×10^{13} cm^{-2} and 1×10^{14} cm^{-2}. The surface area of heavy p+ doping **1460** is confined to the very narrow and long strip of width extending between edge **1478** of the top oxide and the edge of the N+ diffusion **1402**, and running the length of the drain diffusion strip. Note that the thick oxide **1462** prevents penetration of the boron implant into the drain diffusion strip. This greatly reduces the drain junction capacitance, which is highly desirable for fast reading. Note also that p+ region **1460** is automatically self aligned to drain region **1402** through this process.

[**0123**] 7. Top oxide **1473**, nitride **1474** and thin oxide **1475** are now removed by etching. This etching also reduces the thickness of the oxide layer **1462** protecting the source and drain diffusions. It is desirable to leave this film thickness at not less than approximately 100 nanometers at the completion of this etch step.

[**0124**] 8. The remaining steps can be understood in relation to the structure of **FIG. 14***c*: A gate oxide **1464** is grown over the surface, including the channel regions, separating between the long source/drain diffusion strips (typical oxide thickness between 15 and 40 nanometers). A layer of polysilicon is deposited (thickness between 25 and 400 nanometers), doped N+, masked and etched to form continuous narrow strips of floating gates **1404** mask aligned to run parallel to drain diffusion strips **1402** and to overlap p+ regions **1460**.

[**0125**] 9. A second dielectric **1466**, **1411** is grown or deposited on top of the substrate and floating gate strips, respectively. This can be a layer of silicon dioxide or a combination of thin films of silicon dioxide and silicon nitride, of combined thickness in the range between 20 and 50 nanometers.

[**0126**] 10. A second layer of polysilicon is deposited, doped N+ (or silicided for lower resistivity), masked and etched to form control gates **1409** in long strips running perpendicular to the strips of floating gates and source/drain strips. Each control gate strip is capacitively coupled to the floating gate strips it crosses over through dielectric film **1411** in the areas where the strips overlap each other. Control gates **1409** also control the channel conduction in channel portions L2 not covered by the floating gate strips. Each strip of control gates is now covered by a dielectric isolation film (can be thermally grown oxide).

[**0127**] 11. Using the strips of control gates as a mask, exposed areas of dielectric **1466**, **1411** and of the strips of first polysilicon floating gates are etched away. The resulting structure has long strips, or rows, of control gates, each row overlying several floating gates **1404** where the outer edges of each floating gate are essentially self aligned to the edges defining the width of the control gate strip. These edges are now oxidized or covered with a deposited dielectric to completely insulate each floating gate. Field areas between adjacent rows of cells or between adjacent strips of source and drain regions are now automatically self aligned to the active device areas and do not require space consuming isoplanar oxidation isolation regions. (Of course, it is also possible to fabricate transistor **1400** with source, drain and channel regions defined by the edges of a thick isoplanar oxidation isolation layer, or to rely for field isolation on oxide **1462** grown also in the field regions, see the option described in step 5 above.)

[0128] The Eprom cell of this embodiment has several advantages over the prior art Eprom cells:

[0129] a) Control gate **1409** now runs over a relatively thick oxide **1462** over the source and drain regions. Such a thick oxide is not possible for example with the prior art Eitan cell, where these source and drain regions are formed after, not before, the floating gate is formed. This improves the protection from oxide breakdowns and reduces the parasitic capacitance between control gate and drain.

[0130] b) Control of parameter Lp and of the surface P+ doping concentration in region **1460** is superior to that afforded by the DSA prior art Tanaka cell.

[0131] c) The device sensitivity to misalignment between floating gate and drain is far less than that experienced with the prior art Harari, Samachisa and Masuoka cells.

[0132] d) For a given p+ concentration in the channel region, drain junction capacitance is less with this cell than with all other prior art devices, because p+ region **1460** is very narrowly confined near the drain diffusion.

[0133] e) It is possible to dope p+ region **1460** to very high levels (which significantly enhances the programming efficiency) without unduly raising the conduction threshold voltage in the enhancement series channel region L2. This is particularly useful for Flash EEprom embodiments using this cell for the Eprom part. In such a Flash EEprom, the high initial threshold volage in region Lp controlled by floating gate **1404** (initial Vt can be as high as +5.0V, the supply voltage, or higher), can be easily overcome by erasing the cell to lower threshold voltages. As an Eprom device the initial Vt in the unprogrammed state must not be higher than the control-gate voltage during read, and this requirement sets an upper limit on how high the p+ doping concentration can be. Another limit on the magnitude of p+ doping concentration **1460** is established by the minimum drain voltage necessary for programming. The drain junction avalanche breakdown voltage must be at least as high as this minimum programming voltage.

[0134] II. Self Aligned Split Channel Flash EEprom Cell with Isoplaner Field Isolation

[0135] **FIG. 6***a* presents a topological view of a 2×2 memory array consisting of four Flash EEprom transistors **600***a*, **600***b*, **600***c* and **600***d* in accordance with one embodiment of this invention. **FIG. 6***b* presents a cross section view of the same structure along AA of **FIG. 6***a*. A second cross section along BB results in the Eprom transistor **500***a* shown in **FIG. 5***a*.

[0136] Transistor **600***a* of **FIG. 6***a* is a split channel Eprom transistor which has added to it erase gates **530, 535**, which overlap edges **532***a*, **562***a* of floating gate **504***a*. Transistor **600***a* is programmed as a split channel Eprom transistor having a source diffusion **501***a*, a drain diffusion **502***a*, and a control gate **509**. Floating gate **504***a* and channel portions L1 and L2 are formed in accordance with the split channel Eprom transistor **500***a*of section I.a. or the split channel Eprom transistor **1400** of section I.b. However other split channel Eprom devices (such as the Eitan, Harari, Masuoka or Samachisa prior art Eprom) can also be used for the Eprom structure. The transistor channel width W is defined by the edges **505**, **505***a* of a thick field oxide **562**.

[0137] Transistor **600***a* is erased by tunneling of electrons from floating gate **504***a* to erase gates **530**, **535**, across tunnel dielectrics **531***a*, **561***a* on the sidewalls and top surface of the floating gate where it is overlapped by the erase gate.

[0138] Tunnel dielectric film **531***a*, **561***a* is normally a layer of Silicon Dioxide grown through thermal oxidation of the heavily N+ doped and textured polycrystalline silicon comprising the floating gate. It is well known in the industry (see for example an article by H.A.R. Wegener titled "Endurance Model for textured-poly floating gate memories", *Technical Digest of the IEEE International Electron Device Meeting*, December 1984, p. 480) that such a film, when grown under the appropriate oxidation conditions over properly textured doped polysilicon allows an increase by several orders of magnitude of the conduction by electron tunneling even when the film is several times thicker than tunnel dielectric films grown on single crystal silicon (such as the tunnel dielectric films used in the prior art Samachisa and Kynett devices). For example, a tunnel dielectric oxide grown to a thickness of 40 nanometers on N+ doped and textured polysilicon can conduct by electronic tunneling approximately the same current density as a tunnel dielectric oxide of 10 nanometers thickness grown on N+ doped single crystal silicon under identical voltage bias conditions. It is believed that this highly efficient tunneling mechanism is a result of sharp asperities at the grain boundaries of the polysilicon which is specially textured to enhance the areal density of such asperities. A commonly practices technique is to first oxidize the surface of the polysilicon at a high temperature to accentuate the texturing, then stripping that oxide and regrowing a tunnel oxide at a lower temperature. The oxide film capping such an asperity experiences a local amplification by a factor of four to five of the applied electric field resulting in an efficient localized tunnel injector. The advantage provided by the thicker films of tunnel dielectric is that they are much easier to grow in uniform and defect-free layers. Furthermore the electric field stress during tunneling in the thick (40 nanometer) tunnel dielectric is only 25 percent of the stress in the thin (10 nanometer) tunnel dielectric, assuming the same voltage bias conditions. This reduced stress translates into higher reliability and greater endurance to write/erase cycling. For these reasons, all Flash EEprom embodiments of this invention rely on polypoly erase through a relatively thick tunnel dielectric.

[0139] In the embodiment of **FIGS. 6***a*, **6***b* floating gate **504***a* is formed in a first layer of heavily N+ doped polysilicon of thickness between 25 and 400 nanometers, erase gates **530, 535** are formed in a second layer of N+ doped polysilicon of thickness between 50 and 300 nanometers, and control gate **509** is formed in a third conductive layer of thickness between 200 and 500 nanometers, which may be N+ doped polysilicon or a polycide, a silicide, or a refractory metal. The erase gate can be formed in a relatively thin layer because a relatively high sheet resistivity (e.g., 100 Ohm per square) can be tolerated since almost no current is carried in this gate during tunnel erase.

[0140] The manufacturing process can be somewhat simplified by implementing erase gates **530, 535** in the same

conductive layer as that used for control gate **509**. However the spacing Z between the edges of the control gate and the erase gate (and hence the cell size) would then have to be significantly greater than is the case when the control gate and erase gates are implemented in two different conductive layers insulated from each other by dielectric film **567***a*. In fact, in the triple layer structure **600***a* of **FIG. 6***a* it is even possible to have control gate **509** slightly overlap one or both of the erase gates **530** and **535** (i.e., spacing Z can be zero or negative.) Transistor **600***a* employs a field isolation oxide **562** (**FIG. 6***b*) of thickness between 200 and 1000 nanometers. Gate oxide **564***a* protecting channel portion L**1** (**512***a*) is thermally grown silicon dioxide of thickness between 15 and 40 nanometers. Dielectric film **567***a* which serves to strongly capacitively couple control gate **509** and floating gate **504***a* is grown or deposited. It may be silicon dioxide or a combination of thin films of silicon dioxide and oxidized silicon nitride of combined thickness of between 20 and 50 nanometers. This dielectric also serves as part of the gate oxide protecting channel portion L**2** (**520***a*) as well as insulation **565***a* (**FIG. 5***a*) over the source and drain diffusions. Erase dielectric **531***a*, **561***a* is thermally grown Silicon Dioxide or other deposited dielectrics possessing the appropriate characteristics for efficient erase conduction, such as Silicon Nitride. Its thickness is between 30 and 60 nanometers.

[**0141**] A point of significance is the fact that the tunnel dielectric area contributing to erase in each cell consisting of the combined areas of **531***a* and **561***a*, is insensitive to the mask misalignment between edges **532***a*, **562***a* of floating gate **504***a* and erase gates **530**, **535**. (Note that each erase gate, such as **535**, is shared between two adjacent cells, such as **600***a* and **600***c* in this case). Any such misalignment will result in a reduction of the area of the tunnel dielectric at one edge of the floating gate, but also in an increase of equal magnitude in the area available for tunneling at the other edge of the floating gate. This feature permits the construction of a cell with very small area of tunnel dielectric. By contrast the prior art triple layer Flash EEprom cells of Masuoka and Kuo referenced above are sensitive to mask misalignment and therefore require a structure wherein the nominal area provided for tunnel erase may be much larger than the optimum such area, in order to accommodate for the worst case misalignment condition.

[**0142**] Another distinguishing feature of this embodiment relative to the Masuoka cell of **FIGS. 3***a* and **3***b* is that Masuoka implements the erase gate in a first conductive layer **330**. and the floating gate in a second conductive layer **304**, i.e., in a reverse order to that used in this invention. This results in a far less efficient tunnel erase in the Masuoka cell because the asperities in Masuoka's tunnel dielectric **331** are at the surface of the erase gate (collector) rather than at the injecting surface of the floating gate. Therefore Masuoka's cell requires higher electric fields (and therefore higher V_{ERASE} voltages) than the structure of this invention.

[**0143**] Typical bias voltage conditions necessary to erase memory cells **600***a*, **600***b*, **600***c* and **600***d* are:

[**0144**] V_{ERASE} (on all erase gates **530**, **535**, **536**)=15V to 25V applied for between 100 milliseconds and 10 seconds (the pulse duration is strongly dependent on the magnitude of V_{ERASE}), V_{CG}=0V , V_{BB}=0V. V_D and V_S can be held at 0V or at a higher voltage between 5V and 10V, so as to reduce the net voltage experienced during erase across dielectric film **565***a* in areas such as **563** (**FIG. 6***a*) where erase gate **530** crosses over drain diffusion **502**.

[**0145**] III. Self Aligned Split Channel Flash EEprom Cell with Field Plate Isolation

[**0146**] A 2×2 array of Flash EEprom cells in accordance with another embodiment of this invention is shown in topological view in **FIG. 7***a* and in two cross sectional views AA and CC in **FIGS. 7***b* and **7***c* respectively. Cross sectional view BB is essentially the same as the split channel Eprom transistor of **FIG. 5***a*.

[**0147**] Split channel Flash EEprom transistor **700***a* employs three conductive layers (floating gate **704** erase gates **730**, **735** and control gate **709**) formed in the same sequence as described in section II in conjunction with the Flash EEprom transistor **600***a* of **FIGS. 6***a*, **6***b*. The major distinguishing feature of transistor **700***a* is that erase gates **730**, **735**, **736** are used not only for tunnel erase but also as the switched off gates of isolation field transistors formed outside the active transistor regions. Thus, the thick isoplaner isolation oxide **562** of cell **600***a* (**FIG. 6***b*) is not necessary, and is replaced inside the array of memory cells **700***a*, **700***b*, **700***c* and **700***d* by a much thinner oxide **762** (**FIGS. 7***b*, **7***c*) capped with field plates **730**, **735**, **736**, which are held at OV at all times except during erasing.

[**0148**] The elimination of the thick isoplanar oxide inside the array of memory cells (this isoplanar oxide may still be retained for isolation between peripheral logic transistors) has several advantages:

[**0149**] 1. The surface stress at the silicon-silicon dioxide boundary due to a prolonged thermal isoplanar oxidation cycle is eliminated inside the array, resulting in less leaky source and drain junctions and in higher quality gate oxides.

[**0150**] 2. For a given cell width, the elimination of the isoplanar oxide allows the effective channel width W_1 under floating gate **704** to extend all the way between the two edges **732***a*, **762***a* of the floating gate. By comparison, effective channel width W of transistor **600***a* (**FIG. 6***b*) is determined by the edges **505** of the isoplanar oxide and is therefore substantially smaller. This difference results in a higher read signal for cell **700***a*, or a narrower, smaller cell.

[**0151**] 3. From capacitive coupling considerations (to be discussed in section VI below) the efficiency of tunnel erase is higher in cells where coupling of the floating gate to the silicon substrate **763** is greatest. In transistor **700***a* the entire bottom surface area of the floating gate is tightly coupled to the substrate **763** through the thin gate dielectric **764**. By contrast, in transistor **600***a* (**FIG. 6***b*) much of the bottom surface area of floating gate **504***a* overlies the thick field oxide **562** and is therefore not strongly capacitively coupled to substrate **563**.

[**0152**] 4. The width of control gate **709** between its edges **744** and **774** defines channel width W_2 of the series enhancement channel portion L**2** (**FIG. 7***c*). This permits the reduction in overall cell width due to removal of the requirement for the control gate to overlap the edges of the isoplaner oxide. One precaution necessary in the fabrication of cell **700***a* is that any misalignment between the mask layers defining edge **732***a* of Eloatin g ate **704***a*, edge **784** of erase gate **730**, and edge **744** of control gate **709** must not be

allowed to create a situation where a narrow parasitic edge transistor is created under control gate **709** in parallel with the split channel L1 and L2. However, as with cell **600***a*, since erase gates **730**, **736** and control gate **709** are formed in two separate conductive layers which are isolated from each other by dielectric insulator film **767** (**FIG. 7***b*) there is no requirement placed on the magnitude of the spatial separation Z between edge **784** and edge **744**. In fact, the two edges can be allowed to overlap each other through oversizing or through misalignment, i.e., Z can be zero or negative. Dielectric insulator **767** also forms part of the gate dielectric **766** (**FIG. 7***c*) over channel portion L2.

[**0153**] In a memory array source diffusion **701** and drain diffusion **702** can be formed in long strips. If transistor **500***a* is used as the Eprom transistor, then source diffusion edge **721** is self aligned to the previously discussed sidewall spacer (not shown) while drain diffusion edge **723** is self aligned to edge **722** of floating gate **704***a*. In areas between adjacent floating gates **704***a*, **704***c* the source and drain diffusion edges (**721***x*, **723***x* in **FIG. 7***a*) respectively must be prevented from merging with one another. This can be accomplished by for example first forming floating gates **704***a*, **704***c* as part of a long continuous strip of polysilicon, then using this strip with an associated long continuous strip of sidewall spacer to form by ion implantation long diffusion strips **701**, **702**, removing the spacer strip, and only then etching the long continuous strip of polysilicon along edges **732***a*, **762***a* to form isolated floating gates **704***a*, **704***c*. As with the prior Flash EEprom embodiment it is possible to form this embodiment also in conjunction with Eprom cell **1400** (**FIG. 14***c*) or with any other prior art split channel Eproms so long as they do not have their isoplanar isolation oxide inside the memory array.

[**0154**] IV. Self Aligned Split Channel Flash EEprom Cell with Erase Confined to the Vertical Edges of the Floating Gate.

[**0155**] Another embodiment of the self aligned split channel Flash EEprom of this invention can result in a cell which has smaller area than cells **600***a* and **700***a* of the embodiments described in Sections II and III respectively. In this third embodiment the area for tunnel erase between the floating gate and the erase gate is confined essentially to the surfaces of the vertical sidewalls along the two edges of each floating gate. To best understand how cell **800***a* of this embodiment differs from cell **700***a* a 2×2 array of cells **800***a*, **800***b*, **800***c* and **800***d* are shown in **FIG. 8***a* in topological view and in **FIG. 8***b* along the same cross section direction AA as is the case in **FIG. 7***b* for cells **700***a*, **700***c*.

[**0156**] Cell **800***a* has a floating gate **804***a* formed in a first layer of heavily N+ doped polysilicon. This gate controls the transistor conduction in channel portion L1 (**FIG. 8***a*) through gate oxide insulation film **864**. Control gate **809** is formed in the second conductive layer, and is insulated from the floating gate by dielectric film **867**, which may be a thermally grown oxide or a combination of thin silicon dioxide and silicon nitride films. Edges **874**, **844** of control gate **809** are used as a mask to define by self aligned etching the edges **862***a*, **832***a* respectively of floating gate **804***a*. Erase gates **830**, **835** are formed in a third conductive layer and are made to overlap edges **832***a*, **862***a* of floating gate **804***a*. Each erase gate such as **830** is shared by two adjacent cells (such as **800***a*, **800***c*).

[**0157**] The erase gates are insulated from control gate **809** by dielectric insulator **897** which is grown or deposited prior to deposition of erase gates **830**, **835**, **836**. Tunnel erase dielectrics **831***a*, **861***a* are confined to the surface of the vertical edges **832***a*, **862***a* of the floating gate **804***a*. Erase gate **830** also provides a field plate isolation over oxide **862** in the field between adjacent devices.

[**0158**] The thickness of all conducting and insulating layers in structure **800** are approximately the same as those used in structure **700***a*. However, because the erase gate is implemented here after, rather than before the control gate, the fabrication process sequence is some-what different. Specifically (see **FIGS. 8***a*, **8***b*):

[**0159**] 1. Floating gates **804***a*, **804***c* are formed in long continuous and narrow strips on top of gate oxide **864**. The width of each such strip is L1 plus the extent of overlap of the floating gate over the drain diffusion.

[**0160**] 2. Dielectric **867** is formed and the second conductive layer (N+ doped polysilicon or a silicide) is deposited.

[**0161**] 3. Control gates **809** are defined in long narrow strips in a direction perpendicular to the direction of the strips of floating gates. The strips are etched along edges **844**, **874**, and insulated with relatively thick dielectric **897**.

[**0162**] 4. Edges **844**, **874** (or the edges of insulator spacer **899** formed at both edges of control gate strip **809**) are then used to etch dielectric **867** and then, in a self aligned manner to also etch vertical edges **832***a* and **862***a* of the underlying floating gate strips, resulting in isolated floating gates which have exposed edges of polysilicon only along these vertical walls.

[**0163**] 5. Tunnel dielectric films **831***a*, **861***a* are formed by thermal oxidation of these exposed surfaces.

[**0164**] 6. A third conductive layer is deposited, from which are formed erase gates **830** in long strips running in between and parallel to adjacent strips of control gates. These erase gates also serve as field isolation plates to electrically isolate between adjacent regions in the memory array.

[**0165**] Flash EEprom transistor **800***a* can be implemented in conjunction with any of the split channel Eprom transistors of this invention (transistors **500***a* and **1400**) or with any of the prior art split gate Eprom transistors of Eitan, Samachisa, Masuoka or Harari. For example, an array of Flash EEprom transistors **800***a* can be fabricated by adding a few process steps to the fabrication process for the split channel Eprom transistor **1400**. (**FIG. 14***c*), as follows:

[**0166**] Steps 1 through 10 are identical to steps 1 through 10 described in Section I.b. in conjunction with the manufacturing process for split channel Eprom transistor **1400**.

[**0167**] Steps 11, 12, and 13 are the process steps 4, 5, and 6 respectivly described in this section IV in conjunction with split channel Flash EEprom transistor **800***a*.

[**0168**] Cell **800***a* results in a very small area of tunnel erase, which is also relatively easy to control (it is not defined by a mask dimension, but rather by the thickness of the deposited layer constituting the floating gates). For this reason, this cell is the most highly scalable embodiment of this invention.

[0169] V. Self Aligned Split Channel Flash EEprom Cell with a Buried Erase Gate.

[0170] A 2×2 array of Flash EEprom cells **900***a*, **900***b*, **900***c* and **900***d* in accordance with a fourth embodiment of this invention is shown in topological view in **FIG. 9***a* and in two cross sectional views AA and DD in **FIGS. 9***b* and **9***c* respectively. Cross section BB of **FIG. 9***a*yields the split channel Eprom structure **500***a* of **FIG. 5***a*.

[0171] Transistor **900***a* is a split channel Flash EEprom transistor having channel portions L**1** and L**2** formed by self alignment as in Eprom transistor **500***a* or in a non self aligned manner as in Eprom transistor **1400**. Erase gate **930** is a narrow conductive strip sandwiched between floating gate **904***a* on the bottom and control gate **909** on top. Erase gate **930** is located away from edges **932***a*, **962***a* of the floating gate. These edges therefore play no role in the tunnel erase, which takes place through tunnel dielectric **931** confined to the area where erase gate **930** overlaps floating gate **904***a*. Erase gate **930** also overlaps a width W_e of the series enhancement channel portion L**2**. During read or programming, erase gate **930** is held at OV, and therefore the channel portion of width W_e does not contribute to the read or program current. The only contribution to conduction in channel portion L**2** comes from widths W_p and W_q where the channel is controlled directly by control gate **909**. Channel portion L**1** however sees conduction contributions from all three widths, W_p, W_q and W_e. Edges **932***a*, **962***a* of floating gate **904***a* can be etched to be self aligned to edges **944**, **974** respectively of control gate **909**. This then permits the formation of channel stop field isolation **998**, by implanting a p type dopant in the field regions not protected by the control gate or floating gate (**FIG. 9***b*).

[0172] One advantage of cell **900***a* is that erase gate strips **930**, **936** can be made very narrow by taking advantage of controlled undercutting by for example isotropic etchings of the conductive layer forming these strips. This results in a small area of tunnel erase, which is insensitive to mask misalignment. Furthermore the channel width W_p and W_q is also insensitive to mask misalignment. This embodiment of Flash EEprom can also be implemented in conjunction with prior art split channel Eproms cells such as the Eitan, Harari, Samachisa or Masuoka cells.

[0173] VI. Device Optimization

[0174] **FIG. 10** represents a schematic of the major capacitances which couple the floating gate of the split channel Flash EEprom cells of this invention to the surrounding electrodes.

[0175] Specifically these are:

[0176] C_G=Capacitance between Floating gate **1104** and control gate **1109**.

[0177] C_D=Capacitance between Floating gate **1104** and drain diffusion **1102**.

[0178] C_B=Capacitance between Floating gate **1104** and substrate **1163**.

[0179] C_E=Capacitance between Floating gate **1104** and erase gate **1130**.

[0180] $C_T=C_G+C_D+C_B+C_E$ is the total capacitance. Q is the net charge stored on the floating gate. In a virgin device, Q=0. In a programmed device Q is negative (excess electrons) and in an erased device Q is positive (excess holes).

[0181] The voltage V_{FG} on Floating gate **1104** is proportional to voltages V_{CG}, V_{ERASE}, V_D, V_{BB} and to the charge Q according to the following equation:

$$V_{FG} = \frac{Q + V_{CG}C_G + V_{ERASE}C_E + V_DC_D + V_{BB}C_B}{C_T} \quad (1)$$

[0182] In all prior art Eprom and Flash EEprom devices as well as in embodiment **600***a* of this invention, the dominant factor in C_T is C_G, the coupling to the control gate. However, in embodiments **700***a*, **800***a* and **900***a* C_B is also a major contributor by virtue of the fact that the entire bottom surface of the floating gate is strongly coupled to the substrate.

[0183] a. Electrical Erase

[0184] During erase, the typical voltage conditions are V_{CG}=OV, V_D=OV, V_S=OV, V_{BB}=OV and V_{ERASE}=20V. Therefore, substituting in equation (1),

$$V_{FG}=Q/C_T+20C_E/C_T \quad (2)$$

[0185] The electric field for tunnel erase is given by

$$E_{ERASE}=V_{ERASE}/t-V_{FG}/t \quad (3)$$

[0186] where t is the thickness of the tunnel dielectric. For a given V_{ERASE}, E_{ERASE} is maximized by making V_{FG} small, which, from equation (2) is possible if C_E/C_T is small. Embodiments **700***a*, **800***a* and **900***a* allow this condition to be readily met: C_E is small since the area of tunnel dielectric is small, and C_T is large because both C_G and C_B are large. These embodiments are therefore particularly well suited for efficiently coupling the erase voltage across the tunnel dielectric.

[0187] b. Multistate Storage

[0188] The split channel Flash EEprom device can be viewed as a composite transistor consisting of two transistors **T1** and **T2** in series—**FIG. 11***a*. Transistor **T1** is a floating gate transistor of effective channel length L1 and having a variable threshold voltage V_{T1}. Transistor **T2** has a fixed (enhancement) threshold voltage V_{T2} and an effective channel length L**2**. The Eprom programming characteristics of the composite transistor are shown in curve (a) of **FIG. 11***b*. The programmed threshold voltage V_{tx} is plotted as a function of the time t during which the programming conditions are applied. These programming conditions typically are V_{CG}=12V, V_D=9V, $V_S=V_{BB}$=OV. No programming can occur if either one of V_{CG} or V_D is at OV. A virgin (unprogrammed, unerased) device has V_{T1}=+1.5V and V_{T2}=+1.0V. After programming for approximately 100 microseconds the device reaches a threshold voltage $V_{tx} \geqq +$ 6.0 volts. This represents the off ("0") state because the composite device does not conduct at V_{CG}=+5.0V. Prior art devices employ a so called "intelligent programming" algorithm whereby programming pulses are applied, each of typically 100 microseconds to 1 millisecond duration, followed by a sensing (read) operation. Pulses are applied until the device is sensed to be fully in the off state, and then one to three more programming pulses are applied to ensure solid programmability.

[0189] Prior art split channel Flash EEprom devices erase with a single pulse of sufficient voltage V_{ERASE} and sufficient duration to ensure that V_{T1} is erased to a voltage below V_{T2} (curve b) in **FIG. 11***b*). Although the floating gate transistor may continue to erase into depletion mode operation (line (C) in **FIG. 11***b*), the presence of the series T2 transistor obscures this depletion threshold voltage. Therefore the erased on ("1") state is represented by the threshold voltage $V_{tx}=V_{T2}=+1.0V$. The memory storage "window" is given by $\Delta V=V_{tx}(\text{"0"})-V_{tx}(\text{"1"})=6.0-1.0=5.0V$. However, the true memory storage window should be represented by the full swing of V_{tx} for transistor **T1**. For example, if T1 is erased into depletion threshold voltage $V_{T1}=-3.0V$, then the true window should be given by $\Delta V=6.0-(-3.0)=9.0V$. None of the prior art Flash EEprom devices take advantage of the true memory window. In fact they ignore altogether the region of device operation (hatched region D in **FIG. 11***b*) where V_{T1} is more negative than V_{T2}.

[0190] This invention proposes for the first time a scheme to take advantage of the full memory window. This is done by using the wider memory window to store more than two binary. states and therefore more than a single bit per cell. For example, it is possible to store 4, rather than 2 states per cell, with these states having the following threshold voltage:

[0191] State "3":—$V_{T1}=-3.0V$, $V_{T2}=+1.0V$ (highest conduction)=1, 1.

[0192] State "2":—$V_{T1}=-0.5V$, $V_{T2\ =+1.0}V$ (intermediate conduction)=1, 0.

[0193] State "1":—$V_{T1}=+2.0V$, $V_{T2}=+1.0V$ (lower conduction)=0, 1.

[0194] State "0":—$V_{T1}=+4.5V$, $V_{T2}=+1.0V$ (no conduction)=0, 0.

[0195] To sense any one of these four states, the control gate is raised to $V_{CG}=+5.0V$ and the source-drain current I_{DS} is sensed through the composite device. Since $V_{T2}=+1.0V$ for all four threshold states transistor T_2 behaves simply as a series resistor. The conduction current I_{DS} of the composite transistor for all 4 states is shown as a function of V_{CG} in **FIG. 11***c*. A current sensing amplifier is capable of easily distinguishing between these four conduction states. The maximum number of states which is realistically feasible is influenced by the noise sensitivity of the sense amplifier as well as by any charge loss which can be expected over time at elevated temperatures. Eight distinct conduction states are necessary for 3 bit storage per cell, and 16 distinct conduction states are required for 4 bit storage per cell.

[0196] Multistate memory cells have previously been proposed in conjunction with ROM (Read only Memory) devices and DRAM (Dynamic Random Access Memory). In ROM, each storage transistor can have one of several fixed conduction states by having different channel ion implant doses to establish more than two permanent threshold voltage states. Alternatively, more than two conduction states per ROM cell can be achieved by establishing with two photolithographic masks one of several values of transistor channel width or transistor channel length. For example, each transistor in a ROM array may be fabricated with one of two channel widths and with one of two channel lengths, resulting in four distinct combinations of channel width and length, and therefore in four distinct Conductive states. Prior art multistate DRAM cells have also been proposed where each cell in the array is physically identical to all other cells. However, the charge stored at the capacitor of each cell may be quantized, resulting in several distinct read signal levels. An example of such prior art multistate DRAm storage is described in *IEEE Journal of Solid-State Circuits*, February 1988, p. 27 in an article by M. Horiguchi et al. entitled "An Experimental Large-Capacity Semi-conductor File Memory Using 16-Levels/Cell Storage". A second example of prior art multistate DRAM is provided in *IEEE Custom Integrated Circuits Conference*, May 1988, p. 4.4.1 in an article entitled "An Experimental 2-Bit/Cell Storage DRAM for Macrocell or Memory-on-Logic Applications" by T. Furuyama et al.

[0197] To take full advantage of multistate storage in Eproms it is necessary that the programming algorithm allow programming of the device into any one of several conduction states. First it is required that the device be erased to a voltage V_{T1} more negative than the "3" state (−3.0V in this example). Then the device is programmed in a short programming pulse, typically one to ten microseconds in., duration. Programming conditions are selected such that no single pulse can shift the device threshold by more than one half of the threshold voltage difference between two successive states. The device is then sensed by comparing its conduction current I_{DS} with that of a reference current source I_{REF}, i (i=0, 1, 2, 3) corresponding to the desired conduction state (four distinct reference levels must be provided corresponding to the four states). Programming pulses are continued until the sensed current (solid lines in **FIG. 11***c*) drops slightly below the reference current corresponding to the desired one of four states (dashed lines in **FIG. 11***c*). To better illustrate this point, assume that each programming pulse raises V_{tx} linearly by 200 millivolts, and assume further that the device was first erased to $V_{T1}=-3.2V$. Then the number of programming/sensing pulses required is:

[0198] For state "3" ($V_{T1}=-3.0V$)

[0199] No. of pulses=(3.2−3.0)/0.2=1

[0200] For state "2" ($V_{T1}=-0.5V$)

[0201] No. of pulses=(3.2−0.5)/0.2=14

[0202] For state "1" ($V_{T1}=+2.0V$)

[0203] No. of pulses=(3.2−(−2.0))/0.2=26

[0204] and for state "0" ($V_{T1}=+4.5V$)

[0205] No. of pulses=(3.2−(−4.5))/0.2=39.

[0206] In actual fact shifts in V_{tx} are not linear in time, as shown in **FIG. 11***b* (curve (a)), therefore requiring more pulses than indicated for states "1" and "0". If 2 microseconds is the programming pulse width and 0.1 microseconds is the time required for sensing, then the maximum time required to program the device into any of the 4 states is approximately 39×2+39×0.1=81.9 microseconds. This is less than the time required by. "intelligent programming algorithms" of prior art devices. In fact, with the new programming algorithm only carefully metered packets of electrons are injected during programming. A further benefit of this approach is that the sensing during reading is the same sensing as that during programming/sensing, and the same reference current sources are used in both programming and reading operations. That means that each and

every memory cell in the array is read relative to the same reference level as used during program/sense. This provides excellent tracking even in very large memory arrays.

[0207] Large memory systems typically incorporate error detection and correction schemes which can tolerate a small number of hard failures i.e. bad Flash EEprom cells. For this reason the programming/sensing cycling algorithm can be automatically halted after a certain maximum number of programming cycles has been applied even if the cell being programmed has not reached the desired threshold voltage state, indicating a faulty memory cell.

[0208] There are several ways to implement the multistate storage concept in conjunction with an array of Flash EEprom transistors. An example of one such circuit is shown in **FIG. 11***e*. In this circuit an array of memory cells has decoded word lines and decoded bit lines connected to the control gates and drains respectively of rows and columns of cells. Each bit line is normally precharged to a voltage of between 1.0 V and 2.0 V during the time between read, program or erase. For a four state storage, four sense amplifiers, each with its own distinct current reference levels IREF, **0**, IREF, **1**, IREF, **2**, and IREF, **3** are attached to each decoded output of the bit line. During read, the current through the Flash EEprom transistor is compared simultaneously (i.e., in parallel) with these four reference levels (this operation can also be performed in four consecutive read cycles using a single sense amplifier with a different reference applied at each cycle, if the attendant additional time required for reading is not a concern). The data output is provided from the four sense amplifiers through four Di buffers (D**0**, D**1**, D**2** and D**3**).

[0209] During programming, the four data inputs Ii (I**0**, I**1**, I**2** and I**3**) are presented to a comparator circuit which also has presented to it the four sense amp outputs for the accessed cell. If Di match Ii, then the cell is in the correct state and no programming is required. If however all four Di do not match all four Ii, then the comparator output activates a programming control: circuit. This circuit in turn controls the bit line (VPBL) and word line (VPWL) programming pulse generators. A single short.programming pulse is applied to both the selected word line and the selected bit line. This is followed by a second read cycle to determine if a match between Di and Ii has been established. This sequence is repeated through multiple programming/reading pulses and is stopped only when a match is established (or earlier if no match has been established but after a preset maximum number of pulses has been reached).

[0210] The result of such multistate programming algorithim is that each cell is programmed into any one of the four conduction states in direct correlation with the reference conduction states I_{REF}, i. In fact, the same sense amplifiers used during programming/reading pulsing are also used during sensing (i.e., during normal reading). This allows excellent tracking between the reference levels (dashed lines in **FIG. 11***c*) and the programmed conduction levels (solid lines in **FIG. 11***c*), across large memory arrays and also for a very wide range of operating temperatures. Furthermore, because only a carefully metered number of electrons is introduced onto the floating gate during programming or removed during erasing, the device experiences the minimum amount of endurance-related stress possible.

[0211] In actual fact, although four reference levels and four sense amplifiers are used to program the cell into one of four distinct conduction states, only three sense amplifiers and three reference levels are required to sense the correct one of four stored states. For example, in **FIG. 11***c*, I_{REF} ("2") can differentiate correctly between conduction states "3" and "2", I_{REF}("**1**") can differentiate correctly between conduction states "2" and "**1", and I**$_{REF}$("0") can differentiate correctly between conduction states "1" and "0". In a practical implementation of the circuit of **FIG. 11***e* the reference levels I_{REF}, i (i=0, 1, 2) may be somewhat shifted by a fixed amount during sensing to place them closer to the midpoint between the corresponding lower and higher conduction states of the cell being sensed.

[0212] Note that the same principle employed in the circuit of **FIG. 11***e* can be used also with binary storage, or with storage of more than four states per cell. Of course, circuits other than the one shown in **FIG. 11***e* are also possible. For example, voltage level sensing rather than conduction level sensing can be employed.

[0213] c. Improved Charge Retention

[0214] In the example above, states "3" and "2" are the result of net positive charge (holes) on the floating gate while states "1" and "0" are the result of net negative charge (electrons) on the floating gate. To properly sense the correct conduction state during the lifetime of the device (which may be specified as 10 years at 125° C.) it is necessary for this charge not to leak off the floating gate by more than the equivalent of approximately 200 millivolts shift in V_{T1}. This condition is readily met for stored electrons in this as well as all prior art Eprom and Flash EEprom devices. There is no data in the literature on charge retention for stored holes, because, as has been pointed out above, none of the prior art devices concern themselves with the value V_{T1} when it is more negative than VT_{T2}, i.e., when holes are stored on th floating gate. From device physics considerations alone it is expected that retention of holes trapped on the floating gate should be significantly superior to the retention of trapped electrons. This is because trapped holes can only be neutralized by the injection of electrons onto the floating gate. So long as the conditions for such injection do not exist it is almost impossible for the holes to overcome the potential barrier of approximately 5.0 electronvolts at the silicon-silicon dioxide interface (compared to a 3.1 electron volts potential barrier for trapped electrons).

[0215] Therefore it is possible to improve the retention of this device by assigning more of the conduction states to states which involve trapped holes. For example, in the example above state "1" had V_{T1}=+2.0V, which involved trapped electrons since V_{T1} for the virgin device was made to be V_{T1}=+1.5V. If however V_{T1} of the virgin device is raised to a higher threshold voltage, say to V_{T1}=+3.0V (e.g. by increasing the p-type doping concentration in the channel region **560***a* in **FIG. 5***a*), then the same state "1" with V_{T1}=+2.0V will involve trapped holes, and will therefore better retain this value of V_{T1}. Of course it is also possible to set the reference levels so that most or all states will have values of V_{T1} which are lower than the V_{T1} of the virgin device.

[0216] d. Intelligent Erase for Improved Endurance

[0217] The endurance of Flash EEprom devices is their ability to withstand a given number of program/erase cycles. The physical phenomenon limiting the endurance of prior art

Flash EEprom devices is trapping of electrons in the active dielectric films of the device (see the Wegener article referenced above). During programming the dielectric used during hot electron channel injection traps part of the injected electrons. During erasing the tunnel erase dielectric likewise traps some of the tunneled electrons. For example, in prior art transistor **200** (**FIG. 2**) dielectric **212** traps electrons in region **207** during programming and in region **208** during erasing. The trapped electrons oppose the applied electric field in subsequent write/erase cycles thereby causing a reduction in the threshold voltage shift of V_{tx}. This can be seen in a gradual closure (**FIG. 11***d*) in the voltage "window" between the "0" and "1" states of prior art devices. Beyond approximately 1×10^4 program/erase cycles the window closure can become sufficiently severe to cause the sensing circuitry to malfunction. If cycling is continued the device eventually experiences catastrophic failure due to a ruptured dielectric. This typically occurs at between 1×10^6 and 1×10^7 cycles, and is known as the intrinsic breakdown of the device. In memory arrays of prior art devices the window closure is what limits the practical endurance to approximately 1×10^4 cycles. At a given erase voltage, V_{ERASE}, the time required to adequately erase the device can stretch out from 100 milliseconds initially (i.e. in a virgin device) to 10 seconds in a device which has been cycled through 1×10^4 cycles. In anticipation of such degradation prior art Flash EEprom devices specify a sufficiently long erase pulse duration to allow proper erase after 1×10^4 cycles. However this also results in virgin devices being overerased and therefore being unnecessarily over-stressed.

[**0218**] A second problem with prior art devices is that during the erase pulse the tunnel dielectric may be exposed to an excessively high peak stress. This occurs in a device which has previously been programmed to state "0" (V_{T1}=+4.5V or higher). This device has a large negative Q (see equation (2)). When V_{ERASE} is applied the tunnel dielectric is momentarily exposed to a peak electric field with components from V_{ERASE} as well as from Q/C_T (equations (2) and (3)). This peak field is eventually reduced when Q is reduced to zero as a consequence of the tunnel erase. Nevertheless, permanent and cumulative damage is inflicted through this erase procedure, which brings about premature device failure.

[**0219**] To overcome the two problems of overstress and window closure a new erase algorithm is disclosed, which can also be applied equally well to any prior art Flash EEprom device. Without such new erase algorithm it would be difficult to have a multistate device since, from curve (b) in **FIG. 11***d*, conduction states having V_{T1} more negative than V_{T2} may be eliminated after 1×10^4 to 1×10^5 write/erase cycles.

[**0220**] **FIG. 12** outlines the main steps in the sequence of the new erase algorithm. Assume that a block array of m×n memory cells is to be fully erased (Flash erase) to state "3" (highest conductivity and lowest V_{T1} state). Certain parameters are established in conjunction with the erase algorithm. They are listed in **FIG. 12**: V_1 is the erase voltage of the first erase pulse. V_1 is lower by perhaps 5 volts from the erase voltage required to erase a virgin device to state "3" in a one second erase pulse. t is chosen to be approximately 1/10th of the time required to fully erase a virgin device to state "3". Typically, V_1 may be between 10 and 20 volts while t may be between 10 and 100 milliseconds. The algorithm assumes that a certain small number, X, of bad bits can be tolerated by the system (through for example error detection and correction schemes implemented at the system level. If no error detection and correction is implemented then X=0). These would be bits which may have a shorted or leaky tunnel dielectric which prevents them from being erased even after a very long erase pulse. To avoid excessive erasing the total number of erase pulses in a complete block erase cycling can be limited to a preset number, n_{max}. ΔV is the voltage by which each successive erase pulse is incremented. Typically, ΔV is in the range between 0.25V and 1.0V. For example, if V_1=15.0V and ΔV=1.0V, then the seventh erase pulse will be of magnitude V_{ERASE}=21.0V and duration t. A cell is considered to be fully erased when its read conductance is greater than $I_{"3"}$. The number S of complete erase cyclings experienced by each block is an important information at the system level. If S is known for each block then a block can be replaced automatically with a new redundant block once S reaches 1×10^6 (or any other set number) of program/erase cycles. S is set at zero initially, and is incremented by one for each complete block erase multiple pulse cycle. The value of S at any one time can be stored by using for example twenty bits (2^{20} equals approximately 1×10^6) in each block. That way each block carries its own endurance history. Alternatively the S value can be stored off chip as part of the system.

[**0221**] The sequence for a complete erase cycle of the new algorithm is as follows (see **FIG. 12**):

[**0222**] 1. Read S. This value can be stored in a register file. (This step can be omitted if S is not expected to approach the endurance limit during the operating lifetime of the device).

[**0223**] 1a. Apply a first erase pule with $V_{ERASE}=V_1+n\Delta V$, n=0, pulse duration=t. This pulse (and the next few successive pulses) is insufficient to fully erase all memory cells, but it serves to reduce the charge Q on programmed cells at a relatively low erase field stress, i.e., it is equivalent to a "conditioning" pulse.

[**0224**] 1b. Read a sparse pattern of cells in the array. A diagonal read pattern for example will read m+n cells (rather than m×n cells for a complete read) and will have at least one cell from each row and one cell from each column in the array. The number N of cells not fully erased to state "3" is counted and compared with X.

[**0225**] 1c. If N is greater than x (array not adequately erased) a second erase pulse is applied of magnitude greater by ΔV than the magnitude of the first pulse, with the same pulse duration, t. Read diagonal cells, count N.

[**0226**] This cycling of erase pulse/read/increment erase pulse is continued until either $N\leqq X$ or the number n of erase pulses exceed n_{max}. The first one of these two conditions to occur leads to a final erase pulse.

[**0227**] 2a. The final erase pulse is applied to assure that the array is solidly and fully erased. The magnitude of V_{ERASE} can be the same as in the previous pulse or higher by another increment ΔV. The duration can be between 1t; and 5t.

[**0228**] 2b. 100% of the array is read. The number N of cells not fully erased is counted. If N is less than or equal to X, then the erase pulsing is completed at this point.

[**0229**] 2c. If N is greater than X, then address locations of the N unerased bits are generated, possibly for substitution

with redundant good bits at the system level. If N is significantly larger than X (for example, if N represents perhaps 5% of the total number of cells), then a flag may be raised, to.indicate to the user that the array may have reached its endurance end of life.

[0230] 2d. Erase pulsing is ended.

[0231] 3a. S is incremented by one and the new S is stored for future reference. This step is optional. The new S can be stored either by writing it into the newly erased block or off chip in a separate register file.

[0232] 3b. The erase cycle is ended. The complete cycle is expected to be completed with between 10 to 20 erase pulses and to last a total of approximately one second.

[0233] The new algorithm has the following advantages:

[0234] (a) No cell in the array experiences the peak electric field stress. By the time V_{ERASE} is incremented to a relatively high voltage any charge Q on the floating gates has already been removed in previous lower voltage erase pulses.

[0235] (b) The total erase time is significantly shorter than the fixed V_{ERASE} pulse of the prior art. Virgin devices see the minimum pulse duration necessary to erase. Devices which have undergone more than 1×10^3 cycles require only several more ΔV voltage increments to overcome dielectric trapped charge, which only adds several hundred milliseconds to their total erase time.

[0236] (c) The window closure on the erase side (curve (b) in **FIG. 11***d*) is avoided indefinitely (until the device experiences failure by a catastrophic breakdown) because V_{ERASE} is simply incremented until the device is erased properly to state "3". Thus, the new erase algorithm preserves the full memory window.

[0237] **FIG. 13** shows the four conduction states of the Flash EEprom devices of this invention as a function of the number of program/erase cycles. Since all four states are always accomplished by programming or erasing to fixed reference conduction states, there is no window closure for any of these states at least until 1×10^6 cycles.

[0238] In a Flash EEprom memory chip it is possible to implement efficiently the new erase algorithm by providing on chip (or alternatively on a separate controller chip) a voltage multiplier to provide the necessary voltage V1 and voltage increments ΔV to $n\Delta V$, timing circuitry to time the erase and sense pulse duration, counting circuitry to count N and compare it with the stored value for X, registers to store address locations of bad bits, and control and sequencing circuitry, including the instruction set to execute the erase sequence outlined above.

[0239] VII. Edge Tailored Flash EEprom with New Erase Mechanism

[0240] Flash EEprom embodiments **600***a*, **700***a*, **800***a*, and **900***a* of this invention use tunnel erase across a relatively thick dielectric oxide grown on the textured surface of the polysilicon floating gate. Wegener (see article referenced above) has postulated that asperities—small, bump-like, curved surfaces of diameter of approximately 30 nanometers, enhance the electric field at the injector surface (in this case, the floating gate) by a factor of 4 to 5, thereby allowing efficient tunnel conduction to occur even across a relatively thick tunnel dielectric film (30 to 70 nanometers). Accordingly, there have been in the prior art efforts, through process steps such as high temperature oxidation of the polysilicon surface, to shape the surface of the polysilicon so as to accentuate these asperities. Although such steps are reproducible, they are empirical in nature, somewhat costly to implement, and not well understood.

[0241] A new approach is disclosed in this invention which results in a highly reproducible, enhanced electric field tunnel erase which is more efficient than the asperities method yet simpler to implement in several EEprom and Flash EEprom devices. In this approach, the floating gate layer is deposited in a very thin layer, typically in the range between 25 and 200 nanometers. This is much thinner than floating gates of all prior art Eprom, EEprom or Flash EEprom devices, which typically use a layer of polysilicon of thickness at least 200 nanometers, and usually more like 350 to 450 nanometers. The prior art polysilicon thickness is chosen to be higher than 200 nanometers primarily because of the lower sheet resistivity and better quality polyoxides provided by the thicker polysilicon. In certain prior art devices such as the Eitan split channel Eprom the floating gate also serves as an implant mask (**FIG. 4***b*) and must therefore be sufficiently thick to prevent penetration of the implant ions. Likewise, in the split channel Eproir embodiment **500***a* (**FIG. 5***a*) the spacer formation (**FIGS. 5***b* through **5***f*) cannot be readily implemented if floating gate **504***a* is 100 nanometers or less in thickness. However, Eprom transistor **1400** (**FIG. 14***c*) and Flash EEprom transistors **600***a* (**FIG. 6***a*), **700***a* (**FIG. 7***a*), **800***a* (**FIG. 8***a*) and **900***a* (**FIG. 9***a*) as well as the Kupec prior art transistor **200***b* (**FIG. 2***b*) can all be implemented with a floating gate of thickness 100 nanometers or less to achieve a significant improvement in erase efficiency.

[0242] The reason for going to such a thin layer of polysilicon is that the edges of the floating gate in such a thin layer can be tailored through oxidation to form extremely sharp-tipped edges. The radius of curvature of these tipped edges can be made extremely small and is dictated by the thickness of the thin polysilicon film as well as the thickness of the tunnel dielectric grown. Therefore, tunnel erase from these sharp tips no longer depends on surface asperities but instead is dominated by the tip itself.

[0243] As an illustration of this modification, consider Flash EEprom transistor **800***a* (**FIG. 8***a*) in two different embodiments, a relatively thick floating gate (transistor **800***a* shown in **FIG. 8***b* and **FIG. 16***a*) and the same transistor modified to have a very thin floating gate (transistor **800**M shown in **FIG. 16***b*). In the cross section view of **FIG. 16***a* (corresponding to direction AA of **FIG. 8***a*), floating gate **804***a* is approximately 300 nanometers thick. Its vertical edges **862***a*, **832***a* are shown having a multitude of small asperities at the surface. Each asperity acts as an electron injector during tunnel erase (shown by the direction of the arrows across tunnel dielectric layers **861***a*, **831***a*). Injected electrons are collected by erase gates **835**, **830** which overlap vertical edges **862***a*, **832***a*.

[0244] By contrast, the cross section view of modified transistor **800M** is shown in **FIG. 16***b* (along the same cross section AA of **FIG. 8***a*) shows a transistor with floating gate **804M** of thickness 100 nanometers or less. Dielectric layers **864** and **867** as well as control gate **809** can be the same as in transistor **800***a*.

[0245] During oxidation of the thin vertical edges of floating gate **804**M to form tunnel dielectric layers **861**M, **831**M, both top and bottom surfaces of the thin floating gate at its exposed edges are oxidized. This results in extremely sharp tips **870***l*, **870***r* being formed. These tips serve as very efficient electron injectors (shown by arrows across tunnel dielectrics **861**M, **831**M). Injected electrons are collected as in transistor **800***a* by erase gates **835**, **830**, which overlap these sharp-tipped edges.

[0246] Apart from the very efficient and highly reproducible injector characteristics inherent to the thin floating gate of transistor **800**M there is an additional benefit. in that the capacitance between the floating gate at its tip and the erase gate is much smaller than the corresponding capacitance in all other embodiments, including transistor **800***a*. Therefore, from equations (1), (2) and (3) in section VI.a., since

$C_E \ll C_T$,

Therefore, $V_{FG}=Q/C_T$, and

$E_{ERASE}=(V_{ERASE}-Q/C_T)/t$.

[0247] When Q=0 (virgin device), then

$$E_{ERASE}=V_{ERASE}/t \quad (4)$$

[0248] Equation (4) basically states that when C_E is very small relative to C_T, then essentially 100% of the erase voltage V_{ERASE} is effectively applied across the tunnel dielectric layer of thickness t. This allows a reduction of the magnitude of V_{ERASE} necessary to erase the device. Also, a very small C_E allows all other device capacitances contributing to C_T (in **FIG. 10**) to be made small, which leads to a highly scalable Flash EEprom device. The thinner floating gate also helps to improve metalization step coverage and to reduce the propensity to form polysilicon stringers in the manufacturing process.

[0249] Two other points are worth noting. First, the very thin floating gate should not be overly heavily doped, to avoid penetration of the N+ dopant through polysilicon **804**M and gate dielectric **864**. Since floating gate **804**M is never used as a current conductor, a sheet resistivity of between 100 and 10,000 Ohms per square in quite acceptable.

[0250] Secondly, it is necessary to ensure that the sharp tips of the floating gate are adequately spaced apart or isolated from control gate **809**M as well as substrate **860** or the source or drain diffusions (not shown in **FIG. 16***b*). This is because the sharp tip injection mechanism can be so highly effective that unintended partial erase to these surfaces may take place under the voltage conditions prevailing during device programming (i.e., a "program disturbance" condition). This problem is not necessarily a severe one because, looking again at equations (1), (2) and (3), capacitance components C_G, C_D and C_B are each much larger than C_E and therefore the electric field between the floating gate at its edges and any of these three surfaces is much less than E_{ERASE}. Nevertheless, this should be an important consideration in the actual geometrical layout of any floating gate transistor using a very thin floating gate for edge erase.

[0251] Although a thin floating gate layer provides a relatively straight forward approach to achieving after oxidation sharp-tipped edges, other approaches are possible to achieve sharp-tipped edges even in a relatively thick floating gate layer. For example, in **FIG. 16***c* a relatively thick layer forming floating gate **804** is etched with a reentrant angle of etching. After oxidation, a sharp tip **870** is formed at the top edge, facilitating high field tunneling **861** to the erase gate **830** deposited on top of the tunnel erase dielectric **831**.

[0252] In the device of **FIG. 16***d* the erase gate is deposited before the floating gate. Erase gate **830** is etched so as to create a reentrant cavity close to its bottom surface. Tunnel erase dielectric **831** is then grown, followed by deposition and formation of floating gate **804**. Floating gate **804** fills the narrow reentrant cavity where a sharp tip **870** is formed, which facilitates the high field tunneling **861**. Note that the device of **FIG. 16***d* has asperities formed at the surface of the erase gate whereas all other devices described in this invention have asperities formed at the surfaces of their floating gate.

[0253] VIII. Flash EEprom Memory Array Implementations

[0254] The Flash EEprom cells of this invention can be implemented in dense memory arrays in several different array architectures. The first architecture, shown in **FIG. 15***a*, is the one commonly used in the industry for Eprom arrays. The 3×2 array of **FIG. 15***a* shows two rows and three columns of Flash EEprom transistors. Transistors T**10**, T**11**, T**12** along the first row share a common control gate (word line) and a commmon source S. Each transistor in the row has its own drain D connected to a column bit line which is shared with the drains of all other transistors in the same column. The floating gates of all transistors are adjacent their drains, away from their sources. Erase lines are shown running in the bit line direction (can also run in the word line direction), with each erase line coupled (through the erase dielectric) to the floating gates of the transistors to the left and to the right of the erase line. The voltage conditions for the different modes of operation are shown in Table I (**FIG. 17***a*) for the selected cell as well as for unselected cells sharing either the same row (word line) or the same column (bit line). During block erase of all the cells in the array, all erase lines are brought high. However, it is also possible to erase only sectors of the array by taking V_{ERASE} high for pairs of erase gates only in these sectors, keeping all other erase lines at OV.

[0255] A second Flash EEprom memory array architecture which lends itself to better packing density than the array of **FIG. 15***a* is known as the virtual ground array (for a detailed description of this array architecture, see the Harari patent referenced herein). A topological view of such an array of cells was provided in **FIGS. 6***a*, **7***a*, **8***a* and **9***a*. A schematic representation of a 2×2 virtual ground memory array corresponding to the array of **FIG. 6***a* is shown in **FIG. 15***b*. In a virtual ground array, the source and drain regions are used interchangeably. For example, diffusion **502** is used as the drain of transistor **600***a* and as the source of transistor **600***b*. The term "virtual ground comes from the fact that the ground supply applied to the source is decoded rather than hard-wired. This decoding allows the source to be used interchangeably as ground line or drain. The operating conditions in the virtual ground array are given in Table II (**FIG. 17***b*). They are essentially the same as that for the standard architecture array, except that all source and drain columns of unselected cells are left floating during programming to prevent accidental program disturbance. During reading all columns are pulled up to a low voltage (about

1.5V) and the selected cell alone has its source diffusion pulled down close to ground potential so that its current can be sensed.

[0256] The array can be erased in a block, or in entire rows by decoding the erase voltage to the corresponding erase lines.

[0257] While the embodiments of this invention that have been described are the preferred implementations, those skilled in the art will understand that variations thereof may also be possible. In particular, the split channel Flash EEprom devices **600***a*, **700***a*, **800***a* and **900***a* can equally well be formed in conjunction with a split channel Eprom composite transistor **500***a* having channel portions L**1** and L**2** formed in accordance with the one-sided spacer sequence outlined in **FIGS. 5***b* through **5***f*, or in accordance with Eprom transistor **1400**, or with Eprom transistors formed in accordance with other self-aligning process techniques or, altogether in non self-aligning methods such as the ones employed in the prior art by Eitan, Samachisa, Masuoka and Harari. Therefore, the invention is entitled to protection within the full scope of the appended claims.

1. A method of forming a split-channel electrically programmable read only memory transistor on a semiconductor substrate surface, comprising the steps of:

forming on said surface a floating gate having sidewalls and being electrically isolated by a gate dielectric layer from said substrate,

forming a spacer immediately adjacent only one sidewall of said floating gate and extending a controlled distance over said substrate surface,

forming source and drain regions in said substrate by using said floating gate and said spacer as a mask, whereby a channel region is formed in the substrate under the masked region between the source and drain regions,

removing said spacer, and

forming a control gate extending over at least a portion of the floating gate and substrate channel region that was occupied by said spacer, said control gate being electrically insulated from said floating gate and said substrate, whereby a split-channel electrically programmable read only memory transistor is formed.

2. The method according to claim 1 wherein the step of forming a spacer immediately adjacent only one sidewall of the floating gate includes the steps of:

depositing a thin layer of material over said floating gate and extending a distance beyond said floating gate sidewalls,

anisotropically etching said layer of material for a time to remove it except for first and second portions immediately adjacent opposite sidewalls of said floating gate, and

selectively removing said first portion of material without removal of said second portion, whereby said second portion remains as said spacer.

3. The method according to claim 1 wherein the step of forming a spacer immediately adjacent only one sidewall of the floating gate includes the steps of:

depositing a thin layer of protective material over said floating gate and extending a distance beyond said floating gate sidewalls,

depositing a relatively thick layer of spacer material over said thin layer and extending a distance beyond said floating gate sidewalls,

anisotropically etching said layer of spacer material for a controlled time to remove it except for first and second portions immediately adjacent opposite sidewalls of said floating gate, said first portion also being positioned adjacent the location of said drain region and said second portion being positioned adjacent the location of said source region, and

selectively removing said first portion of material without removal of either one of said second portion and said protective material layer, whereby said second portion remains as said spacer.

4. The method according to claim 2 wherein the step of selectively removing said first portion of material includes the steps of:

covering with a masking layer an area including said second portion of material but not said first portion,

etching away said first portion of material, and

removing said masking layer.

5. The method according to claim 1 comprising the additional steps of:

forming regions of a tunnel erase dielectric layer on each of opposite ends of said floating gate, and

forming a pair of parallel erase gates extending between the source and drain regions and on the tunnel dielectric layers.

6. The method according to claim 5 comprising the additional step of forming a second dielectric to insulate the pair of erase gates from said control gate.

7. The method according to claim 6 wherein the step of forming the control gate includes forming said control gate to extend over only a portion of said floating gate, thereby leaving a portion of said floating gate that is not covered by the control gate, and wherein the step of forming an erase dielectric layer includes the step of forming said layer over the portion of the floating gate not covered by the control gate without forming said layer over a portion of the floating gate over which the control gate extends.

8. The method according to claim 7 wherein the steps of forming the tunnel erase dielectric layer and the erase gates are carried out prior to the steps of forming the second dielectric layer and the control gate.

9. The method according to claim 5 wherein the step of forming a region of a tunnel erase dielectric layer on each of opposite ends of said floating gate includes forming the layers on a top surface of the floating gate, and wherein the step of forming a pair of parallel erase gates includes the step of forming each gate over said top surface with at least one of the tunnel dielectric layers therebetween.

10. The method according to claim 5 wherein the step of forming a region of a tunnel erase dielectric layer on each of opposite ends of said floating gate includes forming the layers along opposite sidewalls thereof, and wherein the step of forming a pair of parallel erase gates includes the step of

forming each gate adjacent one of said sidewalls with one of the tunnel dielectric layers therebetween.

11. The method according to claim 5 wherein each of the steps of forming a floating gate, forming a control gate and forming a pair of erase gates include forming their respective gates in a conductive layer that is different from the others.

12. The method according to claim 10 which includes an additional step of forming a thin layer of dielectric on said substrate on at least the portions where the erase gates are positioned, and wherein the step of forming the erase gates includes forming said erase gates over said thin dielectric layer.

13. The method according to claim 1 which includes an additional step, prior to the step of forming the control gate, of forming an erase gate extending over the floating gate between its side walls with a tunnel dielectric therebetween and across the substrate region that was occupied by the spacer with an insulating layer therebetween, and wherein the step of forming the control gate includes forming the control gate over and around the erase gate over the floating gate and the substrate region that was occupied by the user.

14. A method of forming a split-channel flash electrically erasable and programmable read only memory transistor on a semiconductor substrate surface, comprising the steps of:

forming on said surface a floating gate having opposite sides and opposite ends, said floating gate being electrically insulated from said substrate by a gate dielectric layer,

forming in said substrate a drain region adjacent one side of said floating gate and a source region spaced apart from an opposite side of said floating gate, thereby to form a channel region between the source and drain that has a first channel region under the floating gate a second channel region between the source region and the opposite floating gate side,

forming a control gate extending over at least a portion of the floating gate and said second channel region, said control gate being electrically insulated from said floating gate and said substrate,

forming regions of a tunnel erase dielectric layer on each of opposite ends of said floating gate, and

forming a pair of parallel erase gates extending between the source and drain regions and across the opposite ends of the floating gate on the tunnel dielectric layers.

15. The method according to claim 14 wherein the step of forming the control gate includes forming said control gate to extend over only a portion of said floating gate, thereby leaving a portion of said floating gate that is not covered by the control gate, and wherein the step of forming an erase dielectric layer includes the step of forming said layer over the portion of the floating gate not covered by the control gate without forming said layer over a portion of the floating gate over which the control gate extends.

16. The method according to claim 14 wherein the step of forming a region of a tunnel erase dielectric layer on each of opposite ends of said floating gate includes forming the layers on a top surface of the floating gate, and wherein the step of forming a pair of parallel erase gates includes the step of forming each gate over said top surface with at least one of the tunnel dielectric layers therebetween.

17. The method according to claim 14 wherein the step of forming a region of a tunnel erase dielectric layer on each of opposite ends of said floating gate includes forming the layers along opposite sidewalls thereof, and wherein the step of forming a pair of parallel erase gates includes the step of forming each gate adjacent one of said sidewalls with one of the tunnel dielectric layers therebetween.

18. The method according to claim 17 which includes an additional step of forming a thin layer of dielectric on said substrate on at least the portions where the erase gates are positioned, and wherein the step of forming the erase gates includes forming said erase gates over said thin dielectric layer.

19. The method according to claim 17 wherein the step of forming the floating gate includes forming its said opposite ends to have edges that are very thin and relatively sharp.

20. A method of forming a split-channel flash electrically eraseable and programmable read only memory transistor on a semiconductor substrate surface, comprising the steps of:

forming on said surface a floating gate having opposite sides and opposite ends, said floating gate being electrically insulated from said substrate by a gate dielectric layer,

forming in said substrate a drain region adjacent one side of said floating gate and a source region spaced apart from an opposite side of said floating gate, thereby to form a channel region between the source and drain that has a first channel region under the floating gate a second channel region between the source region and the opposite floating gate side,

forming a region of a tunnel erase dielectric layer on a portion of the surface of said floating gate,

forming an erase gate extending across the floating gate on the tunnel dielectric layer and across the second channel region of the substrate with a dielectric layer therebetween, and

forming over and around the erase gate a control gate extending across the floating gate and second channel region, said control gate being electrically insulated from said floating gate and said substrate.

21-149. (canceled)

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